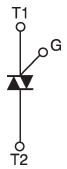
TRIAC (ISOLATED TYPE)

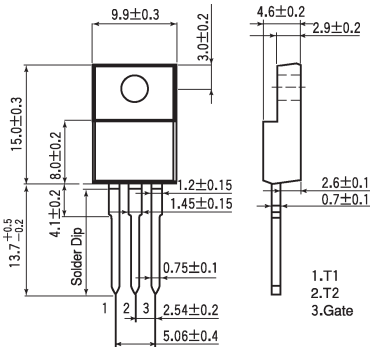
TMG5C40/60F

UL;E76102 (M)

TMG5C40/60F are isolated mold triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 5A
- High surge capability 55A
- Full molded isolated type
- Three types of lead forming





Unit : mm

■Maximum Ratings

(Tj=25℃ unless otherwise specified)

Symbol	Item	Ratings		Unit
		TMG5C40F	TMG5C60F	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V

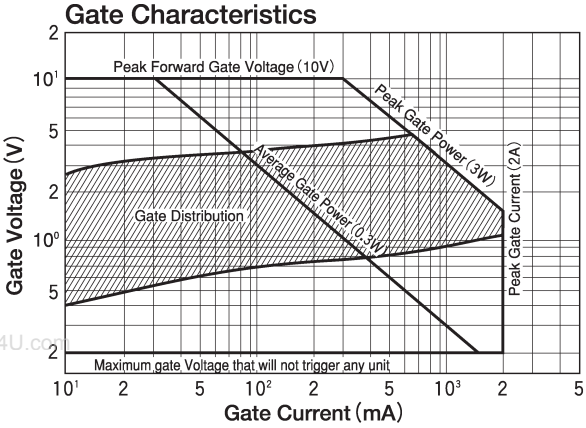
Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc=100℃	5	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	50/55	A
I^2t	I^2t		12.6	A^2S
P_{GM}	Peak Gate Power Dissipation		3	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.3	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
V_{ISO}	Isolation Breakdown Voltage (R.M.S.)	A.C.1 minute	1500	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

■Electrical Characteristics

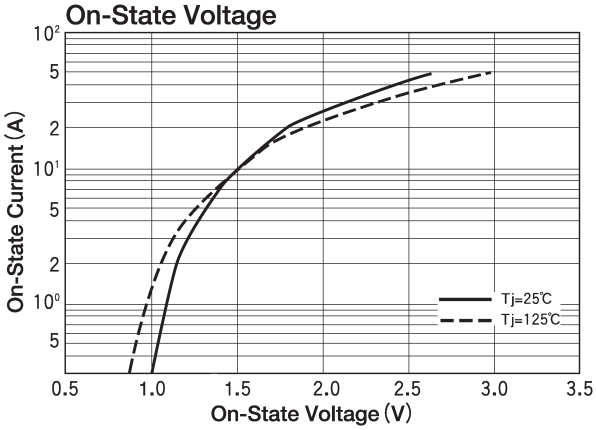
Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	$V_D=V_{DRM}$, Single phase, half wave, Tj=125℃			1	mA
V_{TM}		Peak On-State Voltage	I_T=7A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D=6V, R_L=10Ω			20	mA
I_{GT1}^{-}	2					20	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					20	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D=6V, R_L=10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj=125℃, $V_D=\frac{1}{2}V_{DRM}$	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj=125℃, (di/dt)c=−2.5A/ms, $V_D=\frac{2}{3}V_{DRM}$	5			V/μs
I_H		Holding Current			10		mA
Rth(j-c)		Thermal Impedance	Junction to case			4.0	℃/W

SanRex

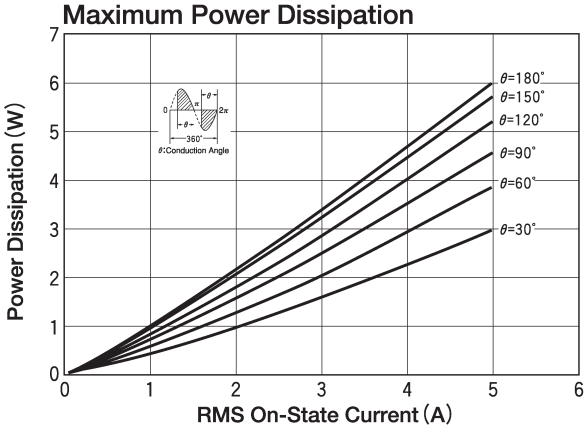
Gate Characteristics



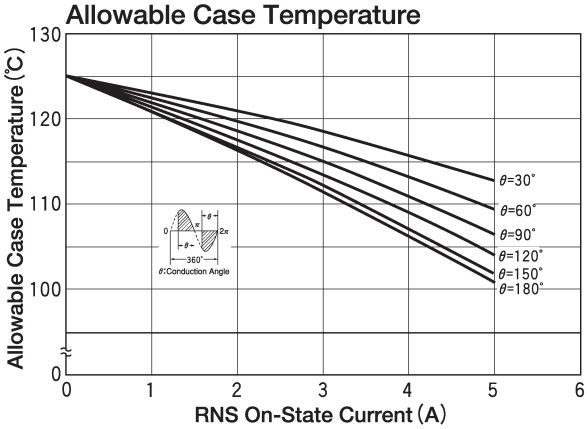
On-State Voltage



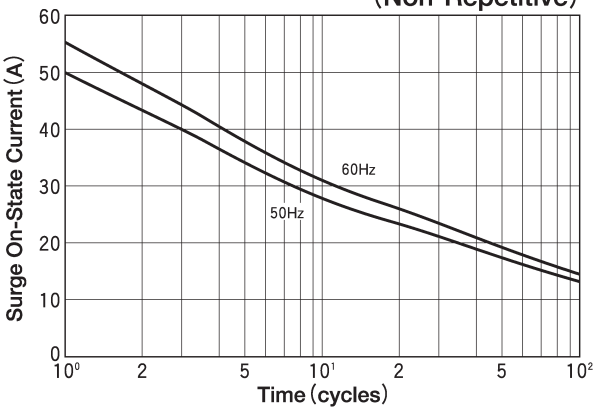
On State Current vs. Maximum Power Dissipation



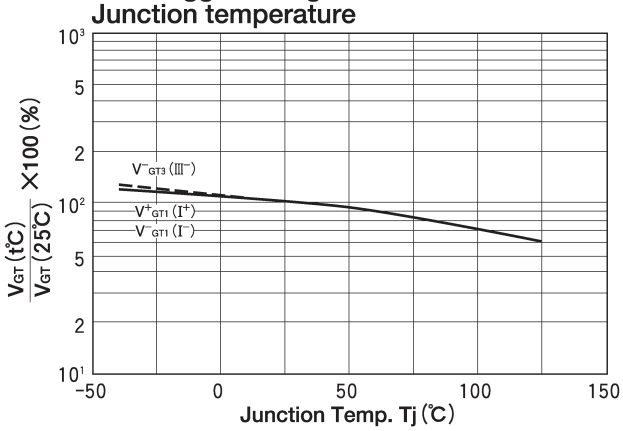
On State Current vs. Allowable Case Temperature



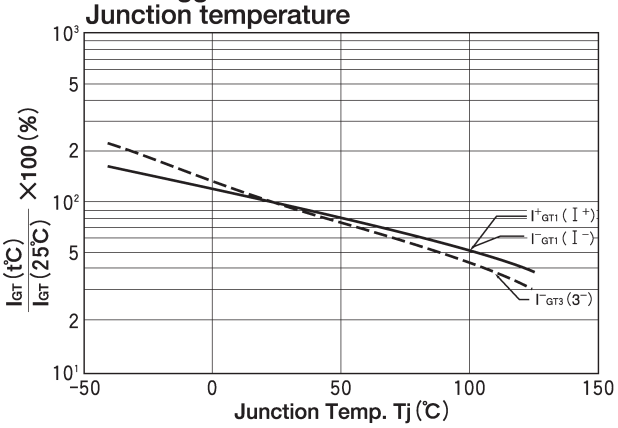
Surge On-State Current Rating (Non-Repetitive)



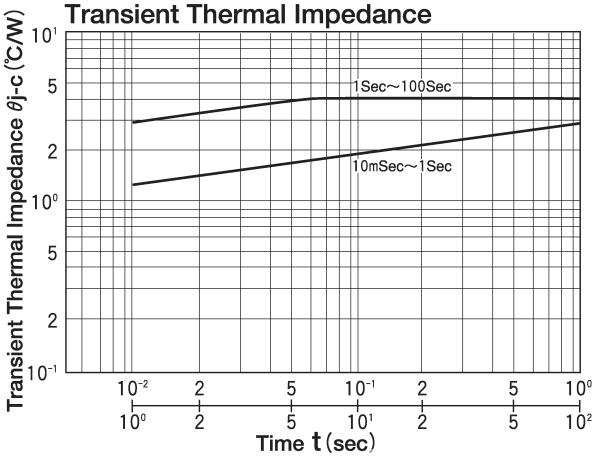
Gate trigger voltage vs. Junction temperature



Gate trigger current vs. Junction temperature



Transient Thermal Impedance

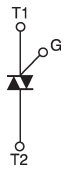


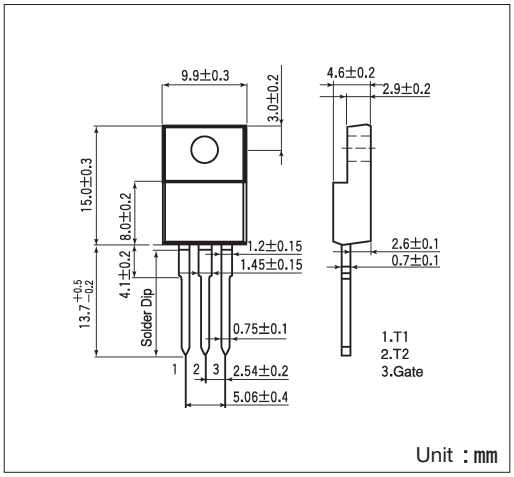
TMG8C40/60F

UL;E76102 (M)

TMG8C40/60F are isolated mold triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 8A
- High surge capability 88A
- Full molded isolated type
- Three types of lead forming





■Maximum Ratings

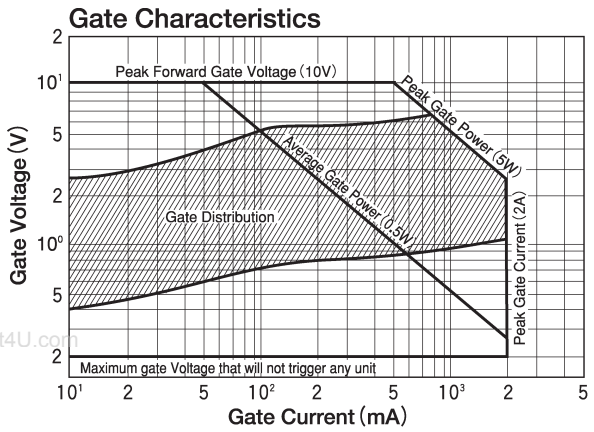
(Tj=25℃ unless otherwise specified)

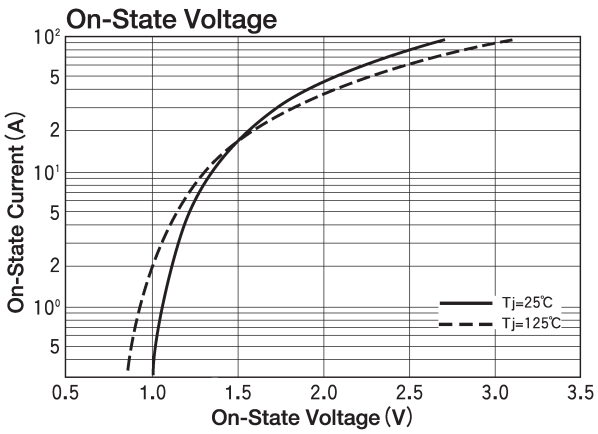
Symbol	Item	Ratings		Unit
		TMG8C40F	TMG8C60F	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V

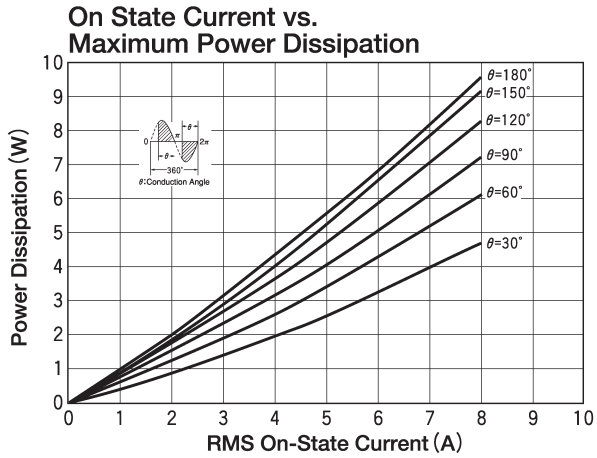
Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc=89℃	8	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	80/88	A
I^2t	I^2t		32	A^2S
P_{GM}	Peak Gate Power Dissipation		5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.5	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
V_{ISO}	Isolation Breakdown Voltage (R.M.S.)	A.C.1 minute	1500	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

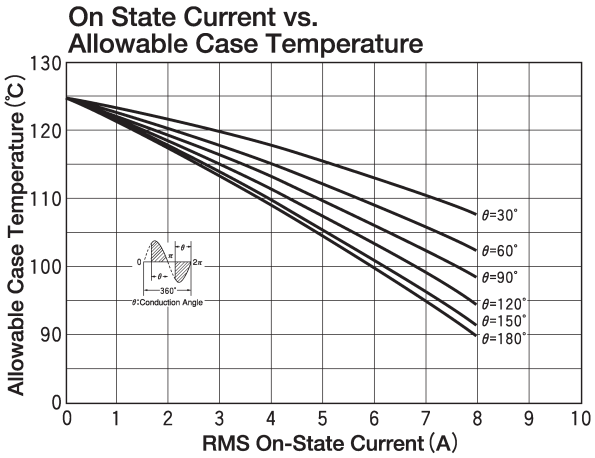
■Electrical Characteristics

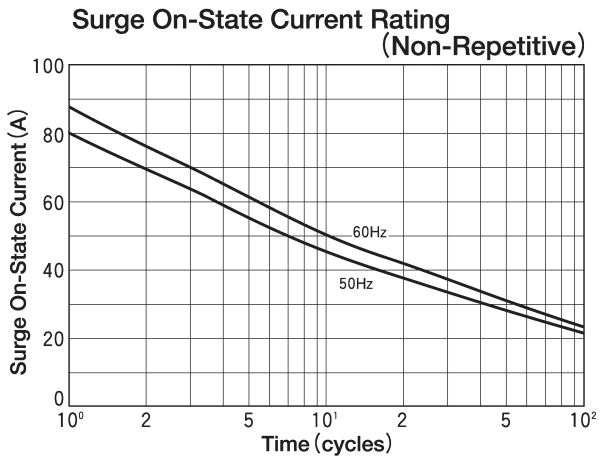
Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	$V_D=V_{DRM}$, Single phase, half wave, Tj=125℃			2	mA
V_{TM}		Peak On-State Voltage	I_T=12A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D=6V, R_L=10Ω			30	mA
I_{GT1}^{-}	2					30	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					30	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D=6V, R_L=10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj=125℃, $V_D=\frac{1}{2}V_{DRM}$	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj=125℃, (di/dt)c=−4A/ms, $V_D=\frac{2}{3}V_{DRM}$	10			V/μs
I_H		Holding Current			15		mA
Rth(j-c)		Thermal Impedance	Junction to case			3.7	℃/W

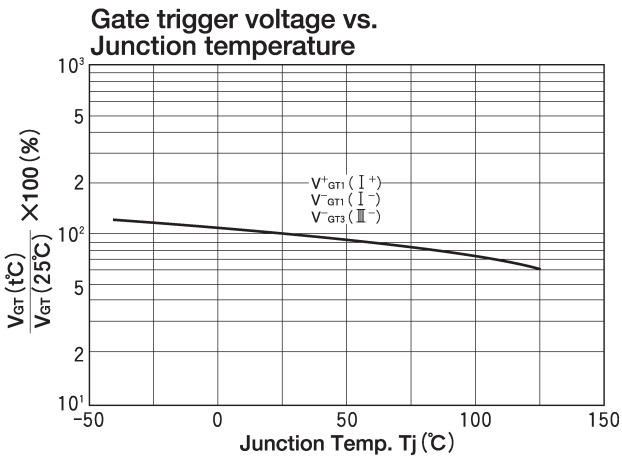


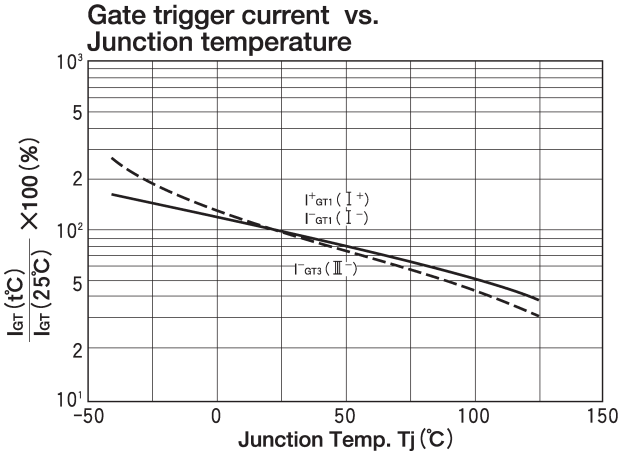


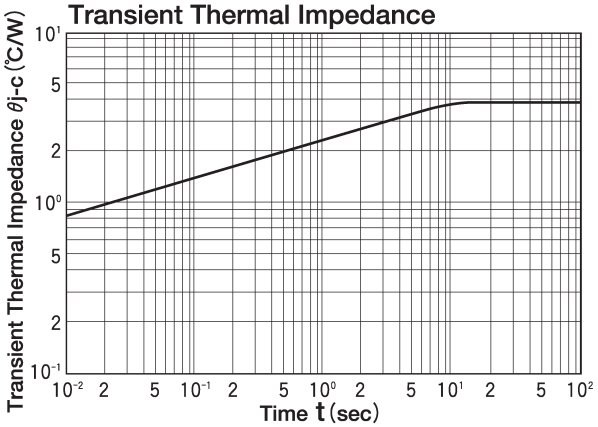










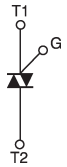


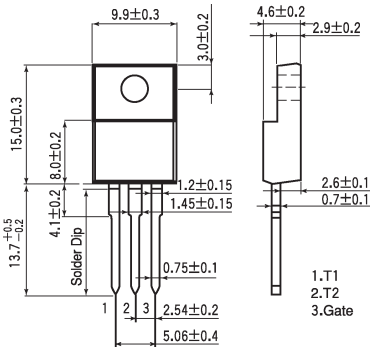
TMG10C40/60F

UL;E76102 (M)

TMG10C40/60F are isolated mold triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 10A
- High surge capability 110A
- Full molded isolated type
- Three types of lead forming





Unit : mm

■Maximum Ratings

(Tj=25℃ unless otherwise specified)

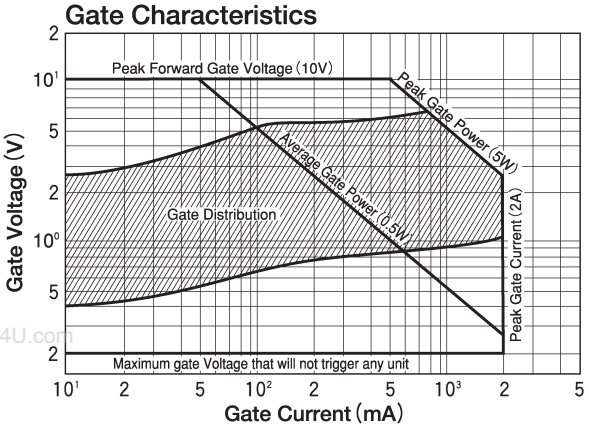
Symbol	Item	Ratings		Unit
		TMG10C40F	TMG10C60F	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc=83℃	10	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	100/110	A
I^2t	I^2t		50	A^2S
P_{GM}	Peak Gate Power Dissipation		5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.5	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
V_{ISO}	Isolation Breakdown Voltage (R.M.S.)	A.C.1 minute	1500	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

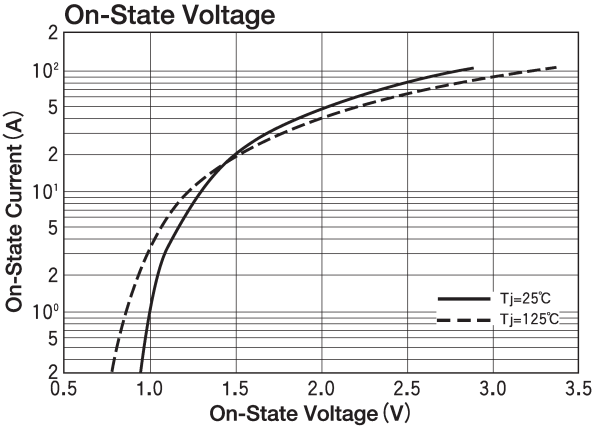
■Electrical Characteristics

Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	$V_D=V_{DRM}$, Single phase, half wave, Tj=125℃			2	mA
V_{TM}		Peak On-State Voltage	I_T=15A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D=6V, R_L=10Ω			30	mA
I_{GT1}^{-}	2					30	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					30	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D=6V, R_L=10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj=125℃, $V_D=\frac{1}{2}V_{DRM}$	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj=125℃, (di/dt)c=−5A/ms, $V_D=\frac{2}{3}V_{DRM}$	10			V/μs
I_H		Holding Current			20		mA
Rth(j-c)		Thermal Impedance	Junction to case			3.5	℃/W

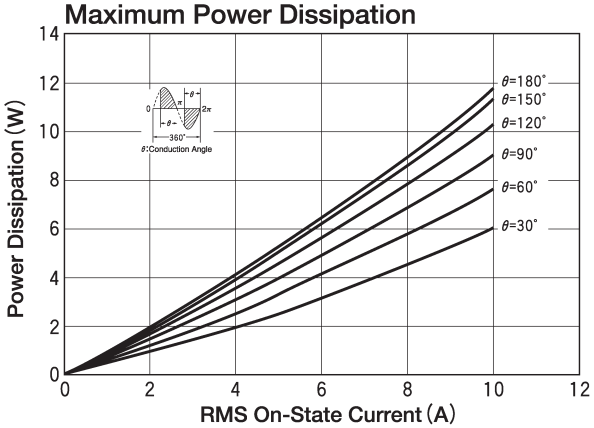
Gate Characteristics



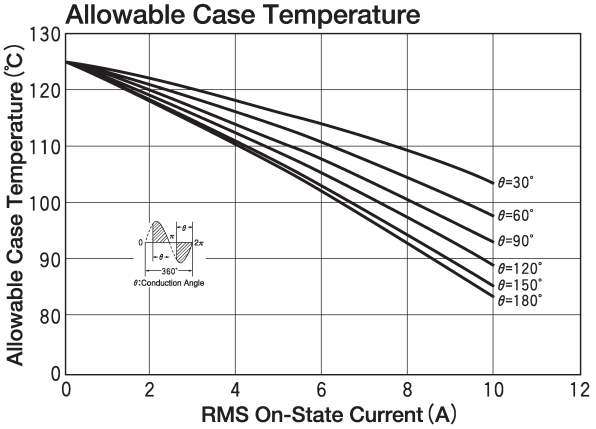
On-State Voltage



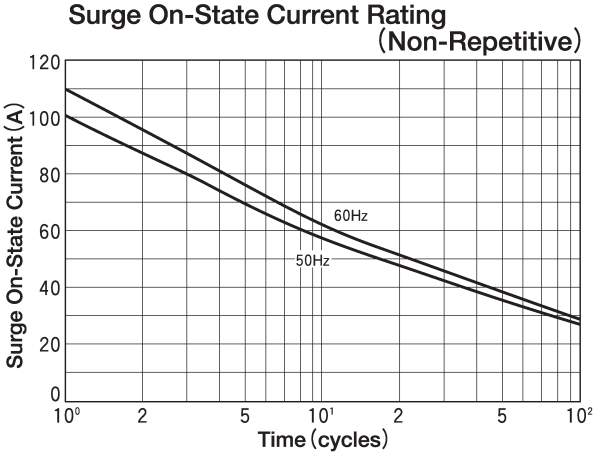
On State Current vs. Maximum Power Dissipation



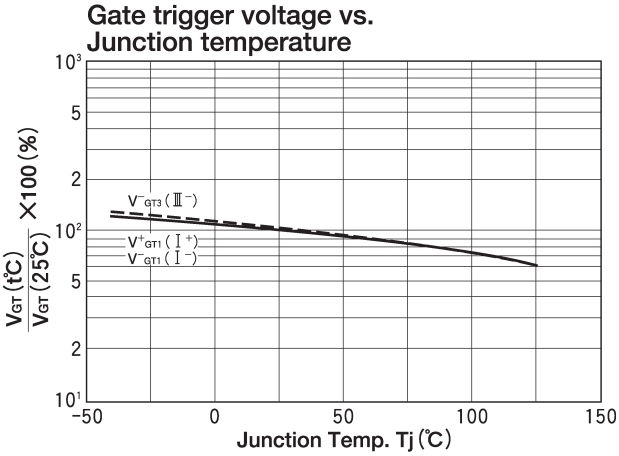
On State Current vs. Allowable Case Temperature



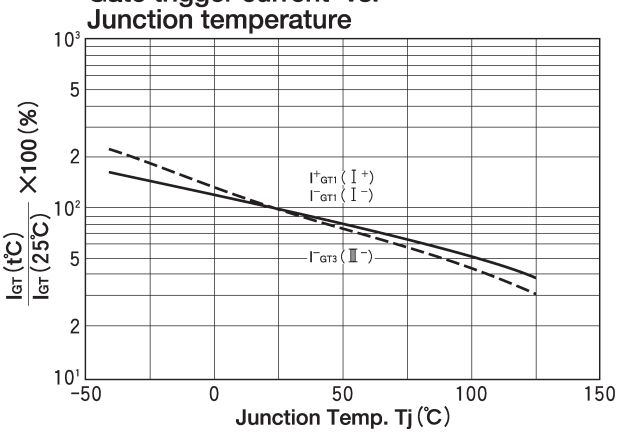
Surge On-State Current Rating (Non-Repetitive)



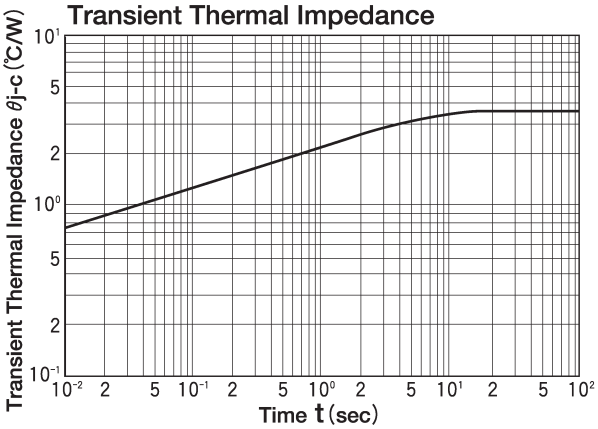
Gate trigger voltage vs. Junction temperature



Gate trigger current vs. Junction temperature



Transient Thermal Impedance



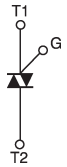
TRIAC(ISOLATED TYPE)

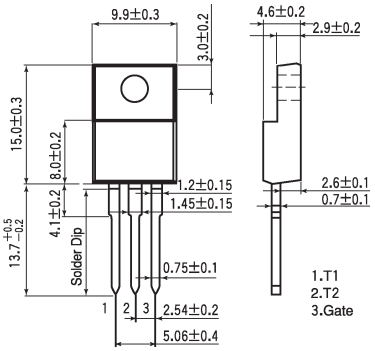
TMG12C40/60F

UL;E76102 (M)

TMG12C40/60F are isolated mold triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 12A
- High surge capability 130A
- Full molded isolated type
- Three types of lead forming





Unit : mm

■Maximum Ratings

(Tj=25℃ unless otherwise specified)

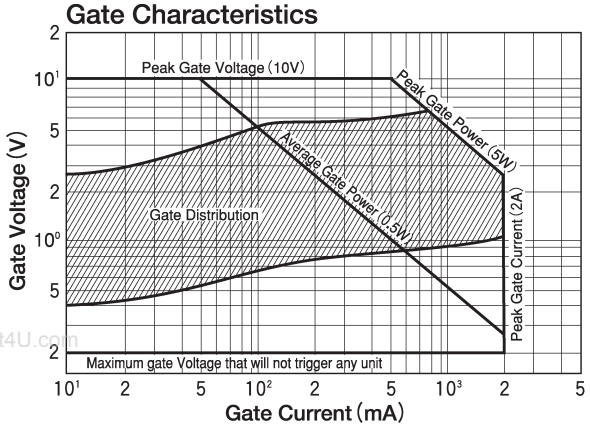
Symbol	Item	Ratings		Unit
		TMG12C40F	TMG12C60F	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc=79℃	12	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	119/130	A
I^2t	I^2t		71	A^2S
P_{GM}	Peak Gate Power Dissipation		5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.5	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
V_{ISO}	Isolation Breakdown Voltage (R.M.S.)	A.C.1 minute	1500	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

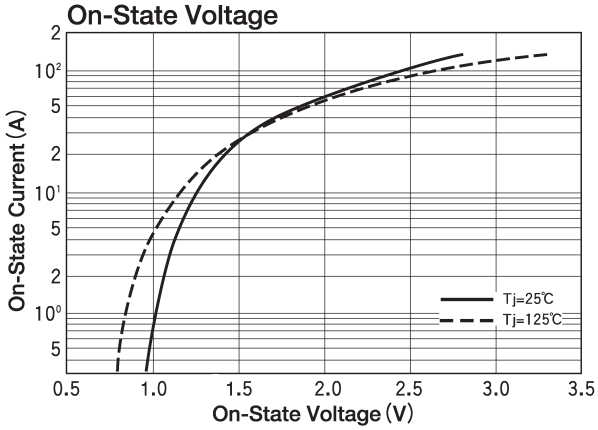
■Electrical Characteristics

Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	$V_D=V_{DRM}$, Single phase, half wave, Tj=125℃			2	mA
V_{TM}		Peak On-State Voltage	I_T=20A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D=6V, R_L=10Ω			30	mA
I_{GT1}^{-}	2					30	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					30	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D=6V, R_L=10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj=125℃, $V_D=\frac{1}{2}V_{DRM}$	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj=125℃, (di/dt)c=−6A/ms, $V_D=\frac{2}{3}V_{DRM}$	10			V/μs
I_H		Holding Current			20		mA
Rth(j-c)		Thermal Impedance	Junction to case			3.3	℃/W

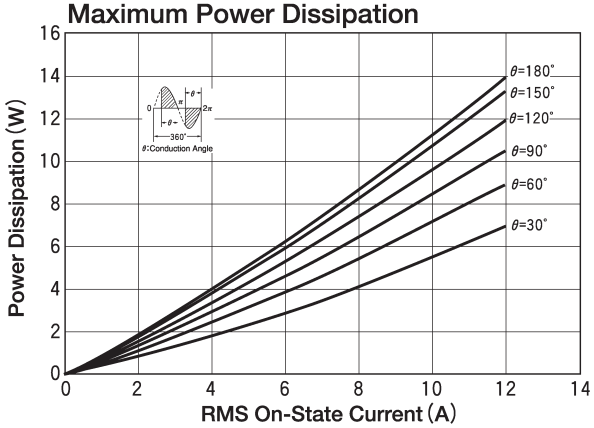
Gate Characteristics



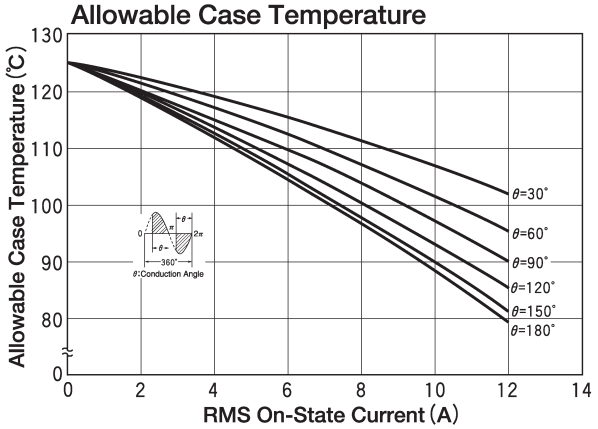
On-State Voltage



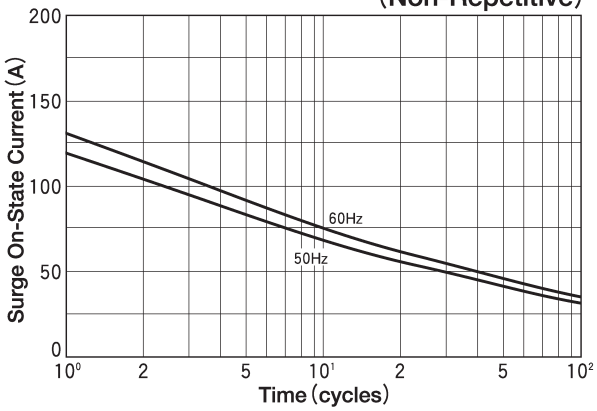
On State Current vs. Maximum Power Dissipation



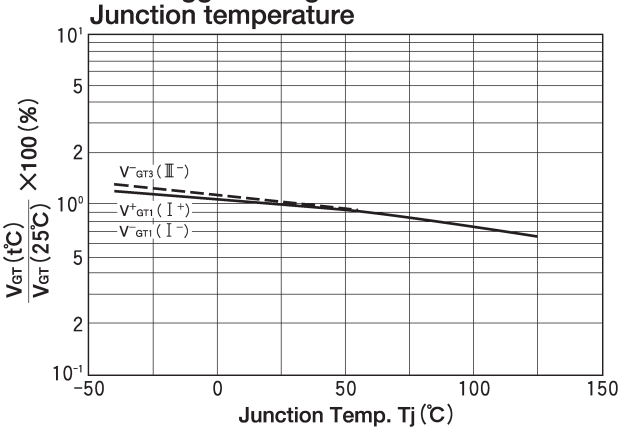
On State Current vs. Allowable Case Temperature



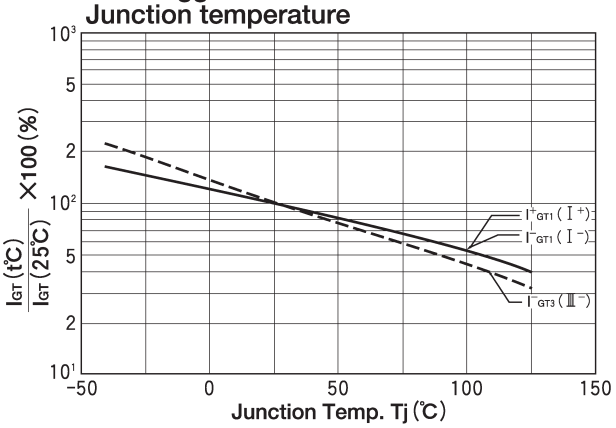
Surge On-State Current Rating (Non-Repetitive)



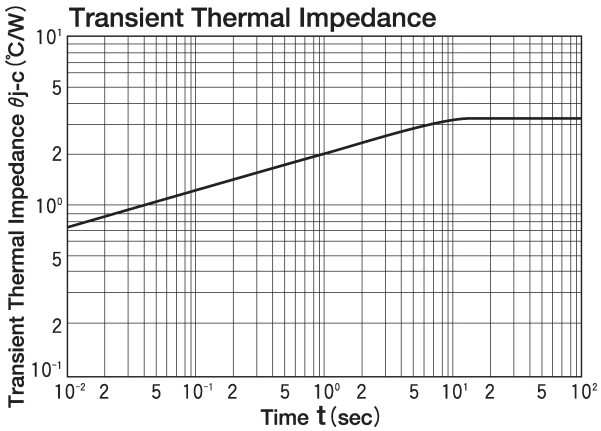
Gate trigger voltage vs. Junction temperature



Gate trigger current vs. Junction temperature



Transient Thermal Impedance

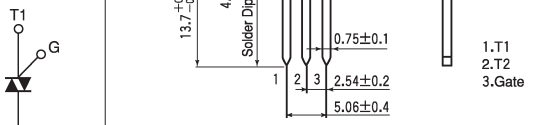


TMG16C40/60F

UL;E76102 (M)

TMG16C40/60F are isolated mold triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 16A
- High surge capability 170A
- Full molded isolated type
- Three types of lead forming



Unit : mm

■Maximum Ratings

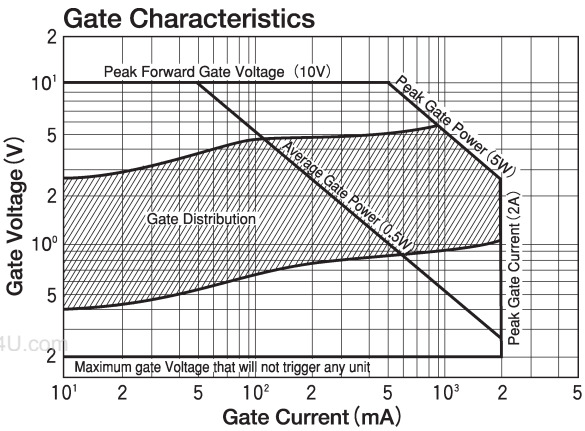
(Tj=25℃ unless otherwise specified)

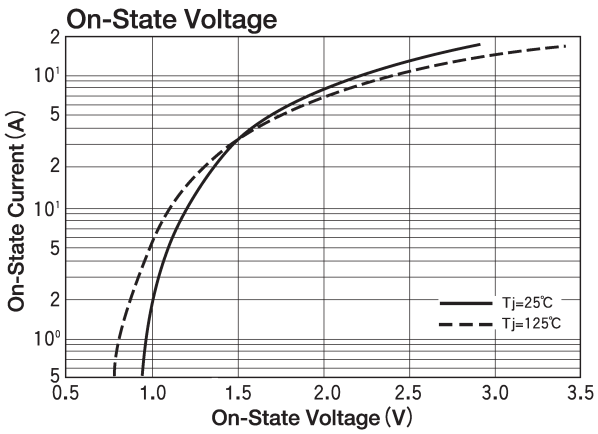
Symbol	Item	Ratings		Unit
		TMG16C40F	TMG16C60F	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V

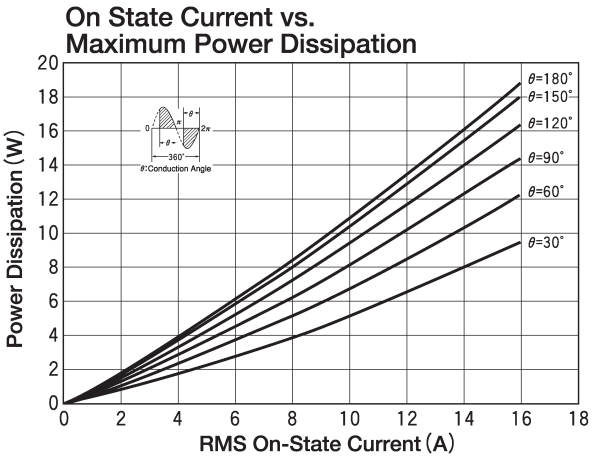
Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc=68℃	16	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	155/170	A
I^2t	I^2t		120	A^2S
P_{GM}	Peak Gate Power Dissipation		5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.5	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
V_{ISO}	Isolation Breakdown Voltage (R.M.S.)	A.C.1 minute	1500	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

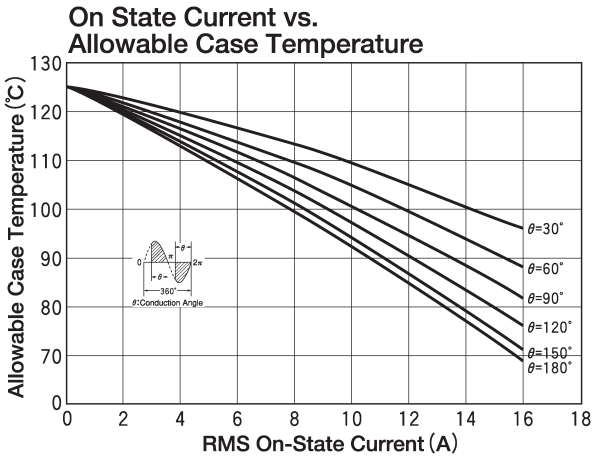
■Electrical Characteristics

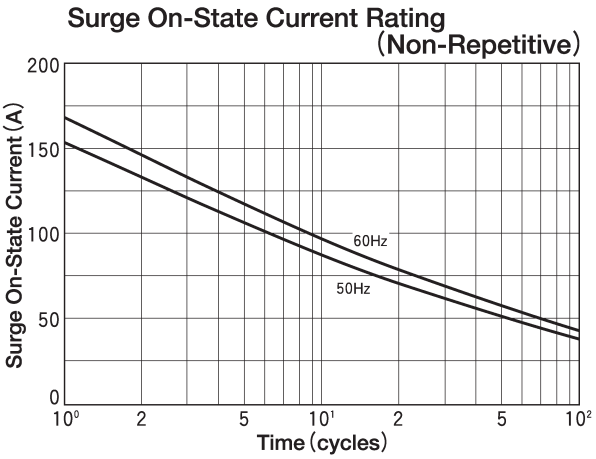
Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	$V_D=V_{DRM}$, Single phase, half wave, Tj=125℃			2	mA
V_{TM}		Peak On-State Voltage	I_T=25A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D=6V, R_L=10Ω			30	mA
I_{GT1}^{-}	2					30	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					30	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D=6V, R_L=10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj=125℃, $V_D=\frac{1}{2}V_{DRM}$	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj=125℃, (di/dt)c=−8A/ms, $V_D=\frac{2}{3}V_{DRM}$	10			V/μs
I_H		Holding Current			25		mA
Rth(j-c)		Thermal Impedance	Junction to case			3.0	℃/W

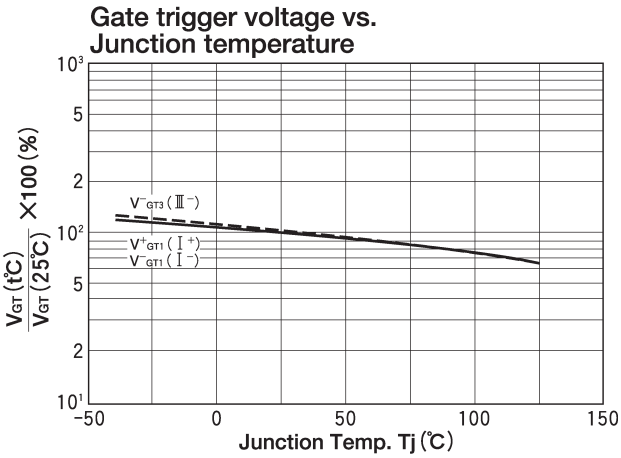


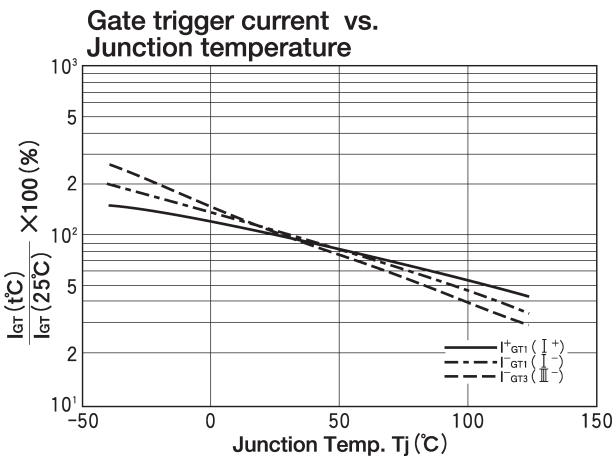


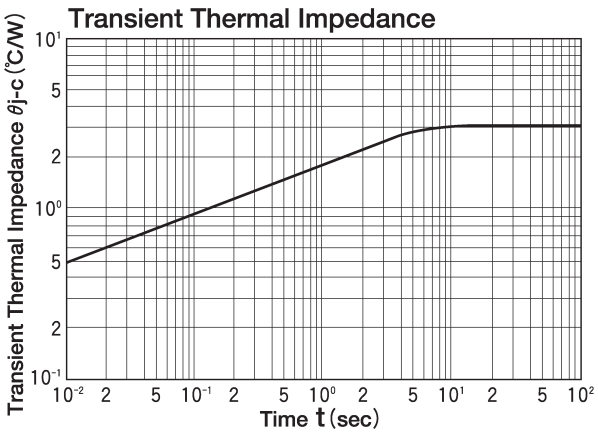








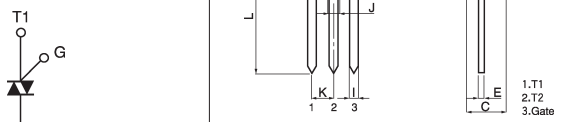




TMG5C60

TMG5C60 are non-isolated triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 5A
- High surge capability 55A
- Non-isolated type



DIM	Millimeters		
	Min	Typ	Max
A	5.58	6.40	7.49
B	8.38	8.60	8.90
C	4.40	4.50	4.70
D	1.15	1.27	1.39
E	0.35	0.45	0.60
F	9.66	10.10	10.28
G	—	16.25	—
H	—	3.83	—
I	0.75	0.85	0.95
J	1.14	1.27	1.40
K	—	2.54	—
L	12.70	13.50	14.27
M	14.48	15.00	15.87

Unit：mm

■Maximum Ratings

(Tj=25℃ unless otherwise specified)

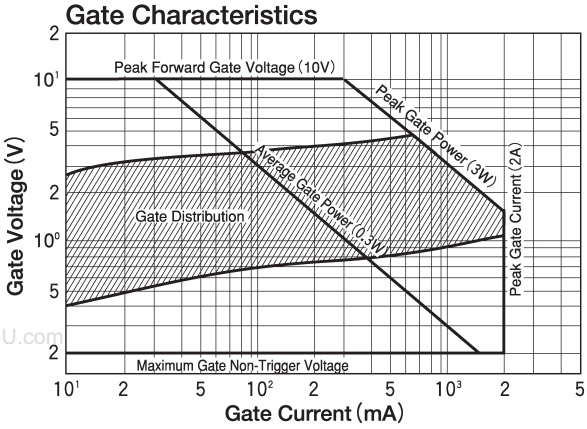
Symbol	Item	Ratings	Unit
		TMG5C60	
V_{DRM}	Repetitive Peak Off-State Voltage	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc＝105℃	5	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	50/55	A
I^2t	I^2t	1ms～10ms	12.6	A^2S
P_{GM}	Peak Gate Power Dissipation		3	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.3	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

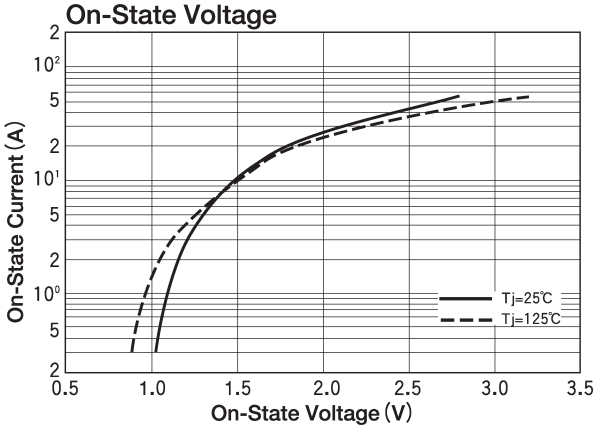
■Electrical Characteristics

Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	V_D=V_{DRM}, Single phase, half wave, Tj＝125℃			1	mA
V_{TM}		Peak On-State Voltage	I_T＝7A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D＝6V, R_L＝10Ω			20	mA
I_{GT1}^{-}	2					20	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					20	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D＝6V, R_L＝10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj＝125℃, V_D＝½V_{DRM}	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj＝125℃, (di/dt)c＝−2.5A/ms, V_D＝⅔V_{DRM}	5			V/μs
I_H		Holding Current			10		mA
Rth(j-c)		Thermal Impedance	Junction to case			3.0	℃/W

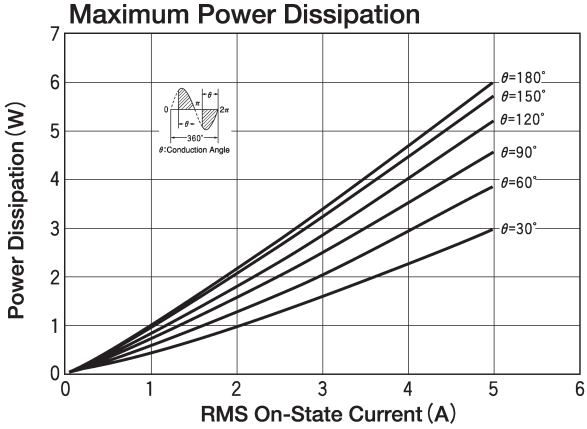
Gate Characteristics



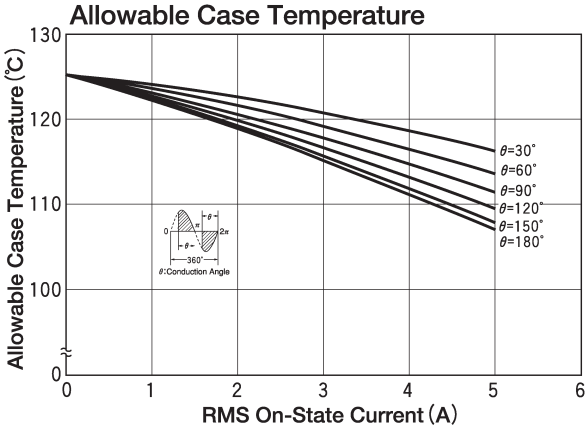
On-State Voltage



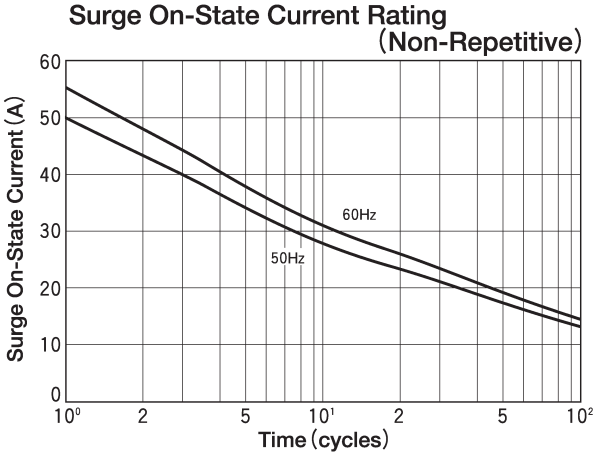
On State Current vs. Maximum Power Dissipation



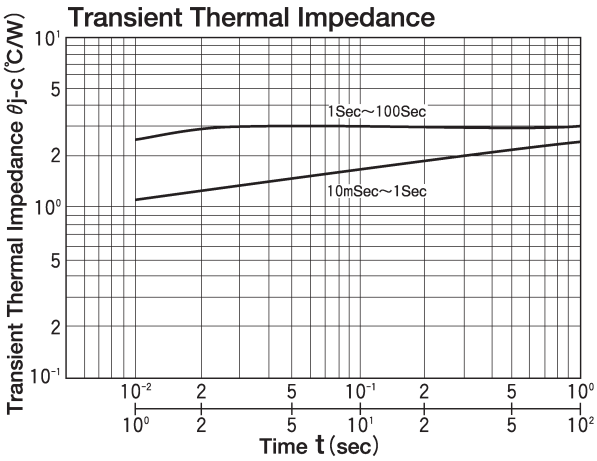
On State Current vs. Allowable Case Temperature



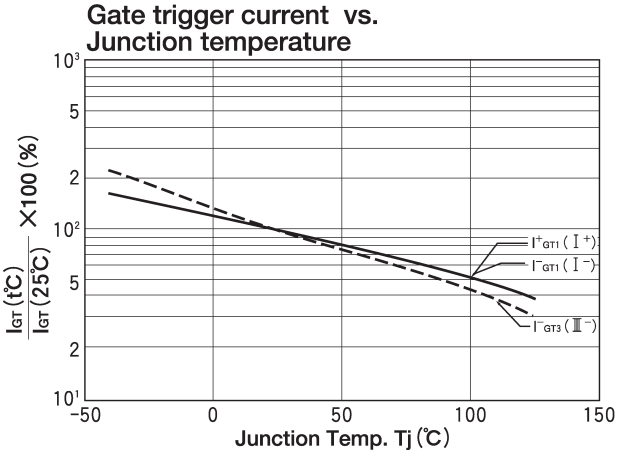
Surge On-State Current Rating (Non-Repetitive)



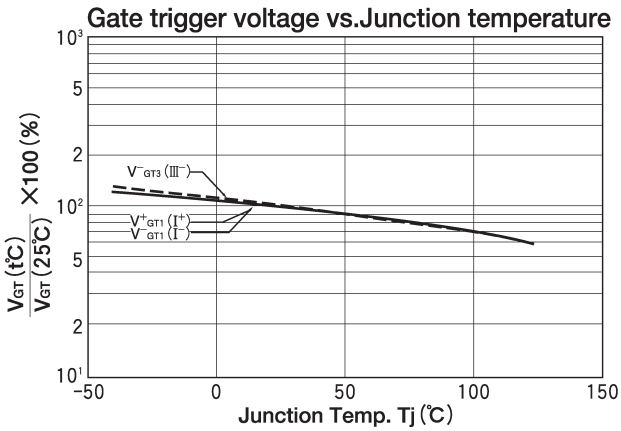
Transient Thermal Impedance



Gate trigger current vs. Junction temperature



Gate trigger voltage vs.Junction temperature

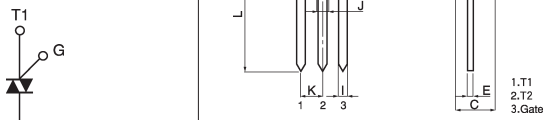


TRIAC（NON-ISOLATED TYPE）

TMG8C60

TMG8C60 are non-isolated triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 8A
- High surge capability 88A
- Non-isolated type



DIM	Millimeters		
	Min	Typ	Max
A	5.58	6.40	7.49
B	8.38	8.60	8.90
C	4.40	4.50	4.70
D	1.15	1.27	1.39
E	0.35	0.45	0.60
F	9.66	10.10	10.28
G	—	16.25	—
H	—	3.83	—
I	0.75	0.85	0.95
J	1.14	1.27	1.40
K	—	2.54	—
L	12.70	13.50	14.27
M	14.48	15.00	15.87

Unit：mm

■Maximum Ratings

（Tj=25℃ unless otherwise specified）

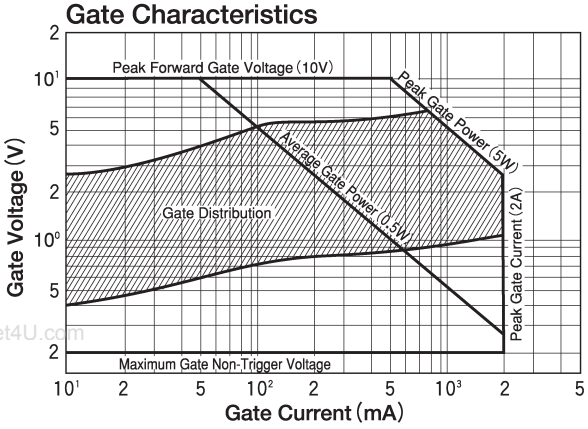
Symbol	Item	Ratings	Unit
		TMG8C60	
V_{DRM}	Repetitive Peak Off-State Voltage	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc＝105℃	8	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	80/88	A
I^2t	I^2t	1ms～10ms	32	A^2S
P_{GM}	Peak Gate Power Dissipation		5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.5	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

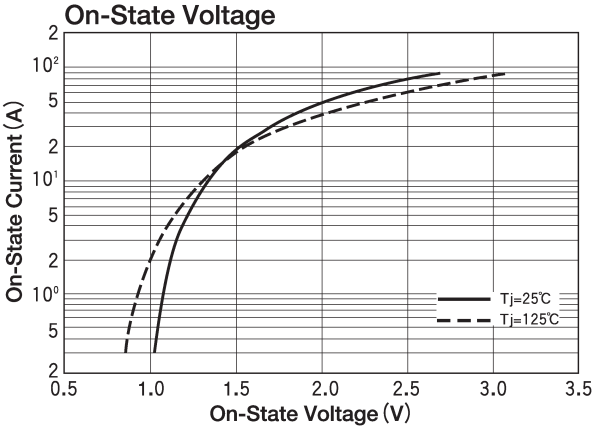
■Electrical Characteristics

Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	V_D=V_{DRM}, Single phase, half wave, Tj＝125℃			2	mA
V_{TM}		Peak On-State Voltage	I_T＝12A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D＝6V, R_L＝10Ω			30	mA
I_{GT1}^{-}	2					30	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					30	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D＝6V, R_L＝10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj＝125℃, V_D＝½V_{DRM}	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj＝125℃, (di/dt)c＝−4A/ms, V_D＝⅔V_{DRM}	10			V/μs
I_H		Holding Current			15		mA
Rth(j-c)		Thermal Impedance	Junction to case			2.0	℃/W

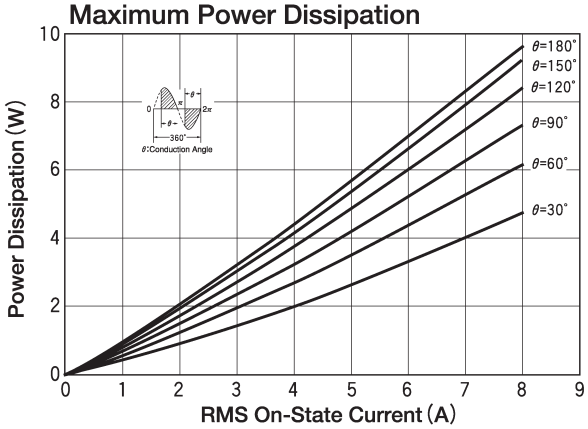
Gate Characteristics



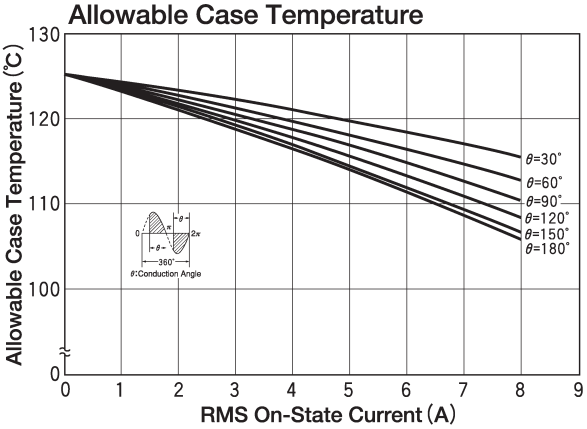
On-State Voltage



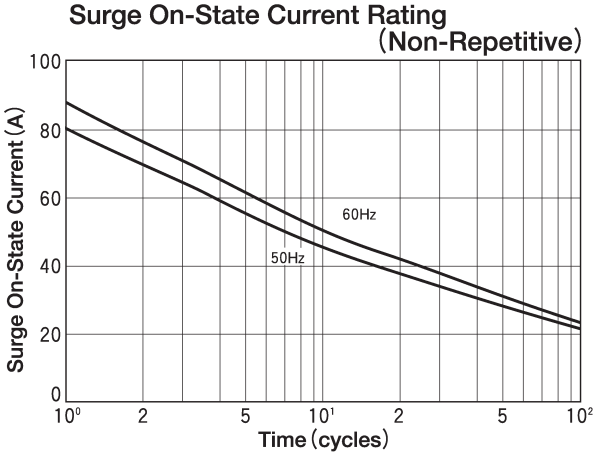
On State Current vs. Maximum Power Dissipation



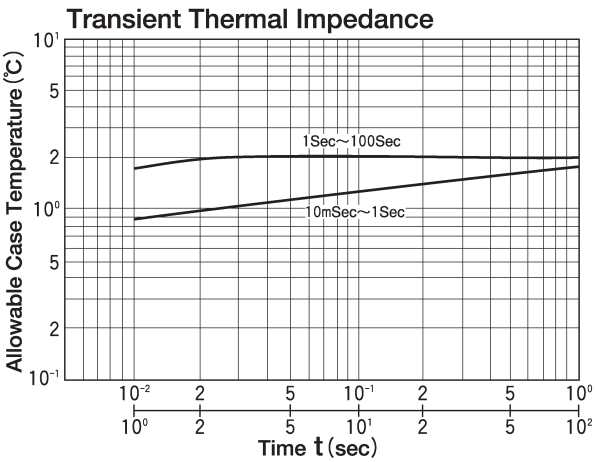
On State Current vs. Allowable Case Temperature



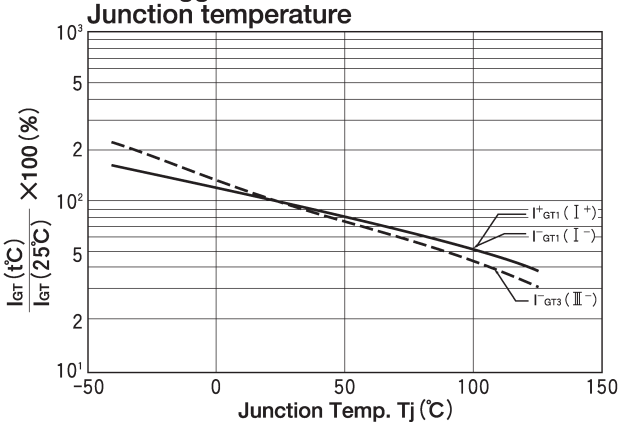
Surge On-State Current Rating (Non-Repetitive)



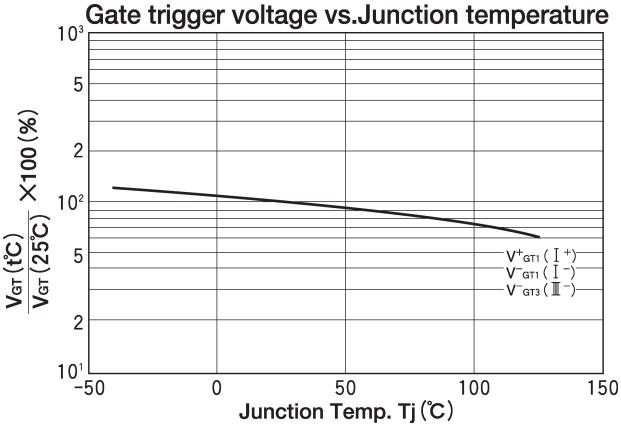
Transient Thermal Impedance



Gate trigger current vs. Junction temperature



Gate trigger voltage vs.Junction temperature

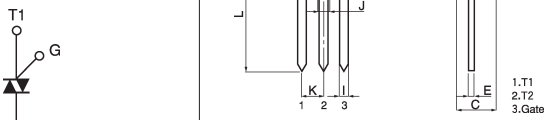


TRIAC（NON-ISOLATED TYPE）

TMG10C60

TMG10C60 are non-isolated triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 10A
- High surge capability 110A
- Non-isolated type



DIM	Millimeters		
	Min	Typ	Max
A	5.58	6.40	7.49
B	8.38	8.60	8.90
C	4.40	4.50	4.70
D	1.15	1.27	1.39
E	0.35	0.45	0.60
F	9.66	10.10	10.28
G	—	16.25	—
H	—	3.83	—
I	0.75	0.85	0.95
J	1.14	1.27	1.40
K	—	2.54	—
L	12.70	13.50	14.27
M	14.48	15.00	15.87

Unit：mm

■Maximum Ratings

（Tj=25℃ unless otherwise specified）

Symbol	Item	Ratings	Unit
		TMG10C60	
V_{DRM}	Repetitive Peak Off-State Voltage	600	V

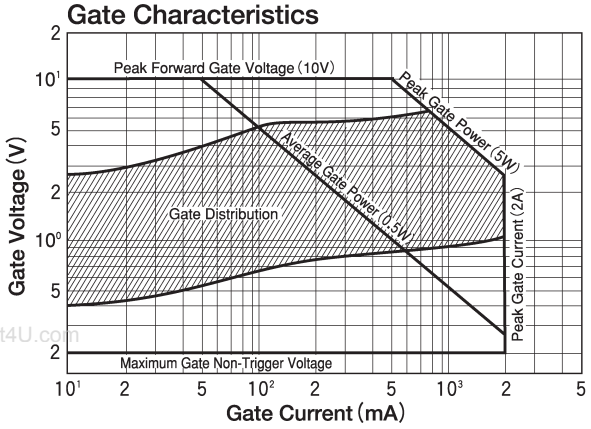
Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc＝103℃	10	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	100/110	A
I^2t	I^2t	1ms～10ms	50	A^2S
P_{GM}	Peak Gate Power Dissipation		5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.5	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

■Electrical Characteristics

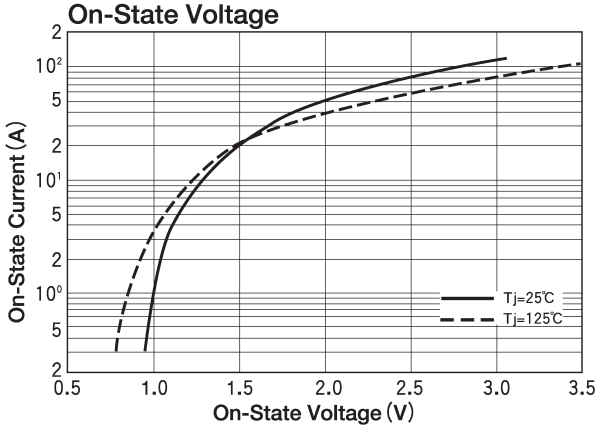
Symbol		Item	Conditions	Ratings			Unit
				Mon.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	V_D=V_{DRM}, Single phase, half wave, Tj＝125℃			2	mA
V_{TM}		Peak On-State Voltage	I_T＝15A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D＝6V, R_L＝10Ω			30	mA
I_{GT1}^{-}	2					30	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					30	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D＝6V, R_L＝10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj＝125℃, V_D＝½V_{DRM}	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj＝125℃, (di/dt)c＝−5A/ms, V_D＝⅔V_{DRM}	10			V/μs
I_H		Holding Current			20		mA
Rth(j-c)		Thermal Impedance	Junction to case			1.8	℃/W

SanRex

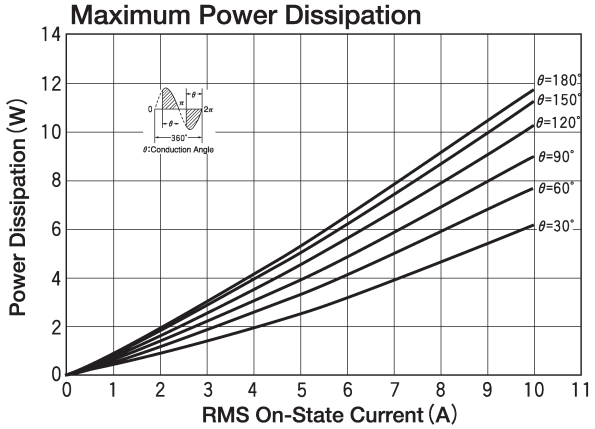
Gate Characteristics



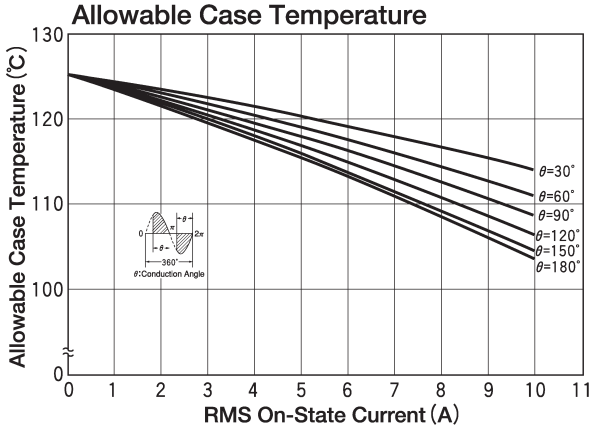
On-State Voltage



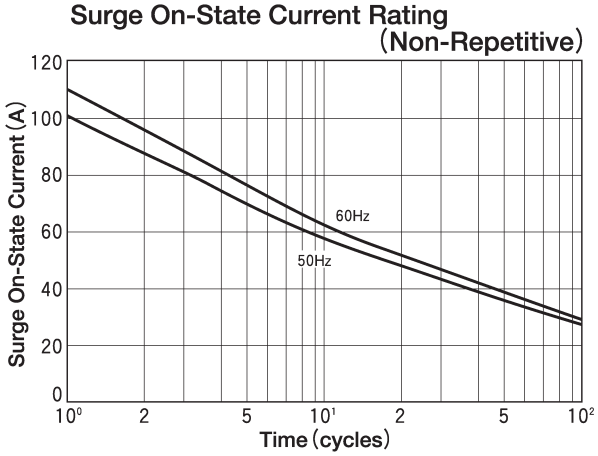
On State Current vs. Maximum Power Dissipation



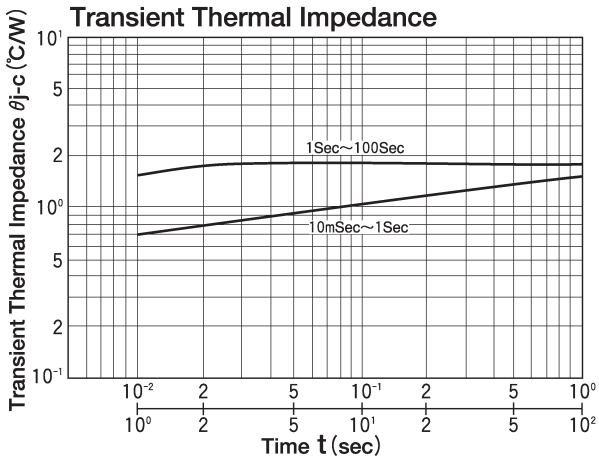
On State Current vs. Allowable Case Temperature



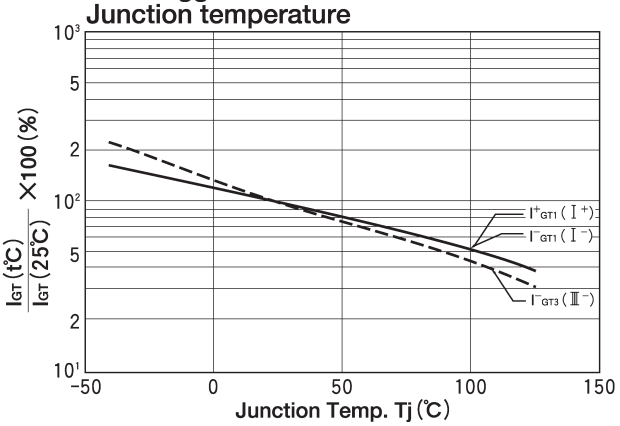
Surge On-State Current Rating (Non-Repetitive)



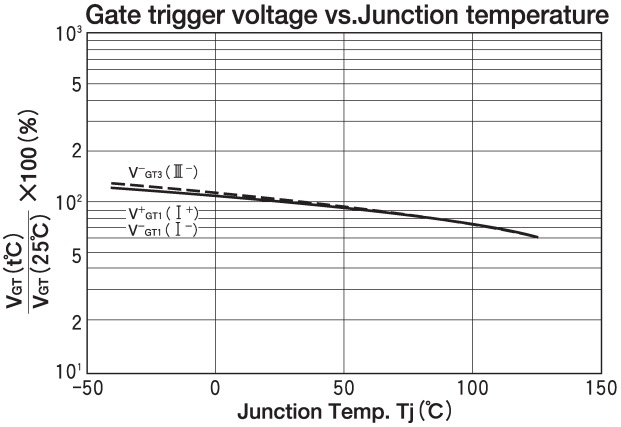
Transient Thermal Impedance



Gate trigger current vs. Junction temperature



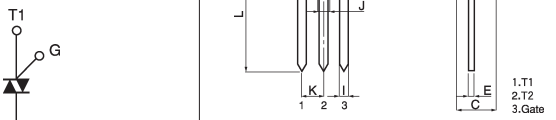
Gate trigger voltage vs.Junction temperature



TMG12C60

TMG12C60 are non-isolated triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 12A
- High surge capability 130A
- Non-isolated type



DIM	Millimeters		
	Min	Typ	Max
A	5.58	6.40	7.49
B	8.38	8.60	8.90
C	4.40	4.50	4.70
D	1.15	1.27	1.39
E	0.35	0.45	0.60
F	9.66	10.10	10.28
G	—	16.25	—
H	—	3.83	—
I	0.75	0.85	0.95
J	1.14	1.27	1.40
K	—	2.54	—
L	12.70	13.50	14.27
M	14.48	15.00	15.87

Unit：mm

■Maximum Ratings

(Tj=25℃ unless otherwise specified)

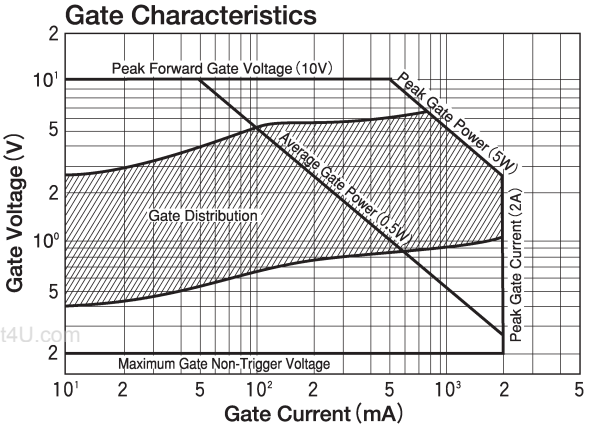
Symbol	Item	Ratings	Unit
		TMG12C60	
V_{DRM}	Repetitive Peak Off-State Voltage	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc＝100℃	12	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	119/130	A
I^2t	I^2t	1ms～10ms	71	A^2S
P_{GM}	Peak Gate Power Dissipation		5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.5	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

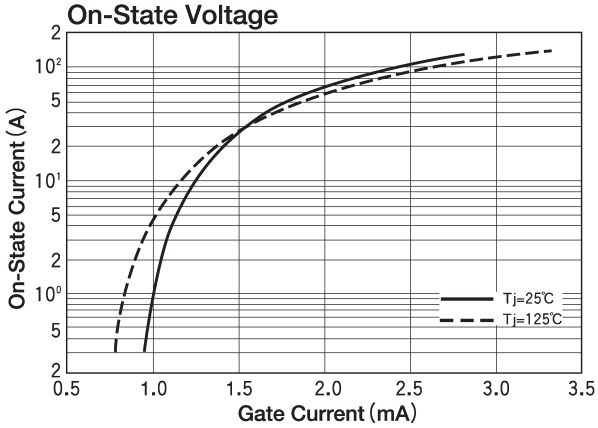
■Electrical Characteristics

Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	V_D=V_{DRM}, Single phase, half wave, Tj＝125℃			2	mA
V_{TM}		Peak On-State Voltage	I_T＝20A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D＝6V, R_L＝10Ω			30	mA
I_{GT1}^{-}	2					30	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					30	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D＝6V, R_L＝10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj＝125℃, V_D＝½V_{DRM}	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj＝125℃, (di/dt)c＝−6A/ms, V_D＝⅔V_{DRM}	10			V/μs
I_H		Holding Current			20		mA
Rth(j-c)		Thermal Impedance	Junction to case			1.8	℃/W

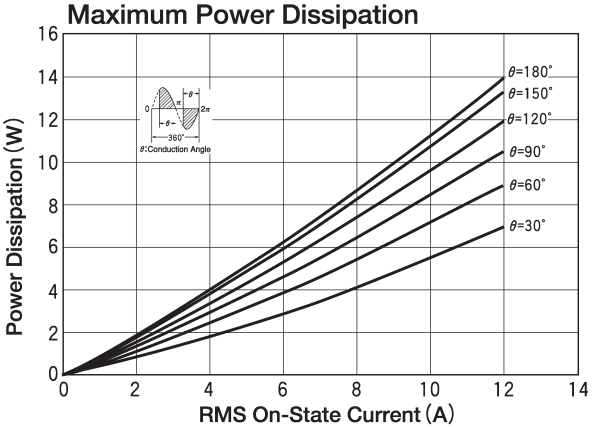
Gate Characteristics



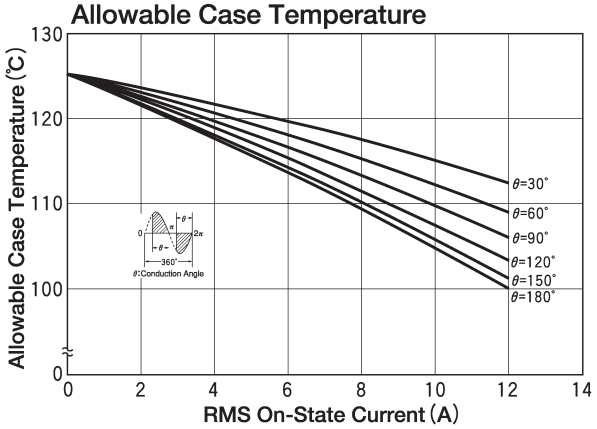
On-State Voltage



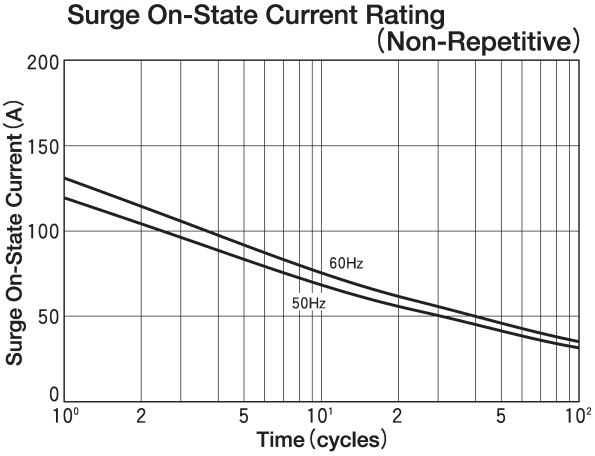
On State Current vs. Maximum Power Dissipation



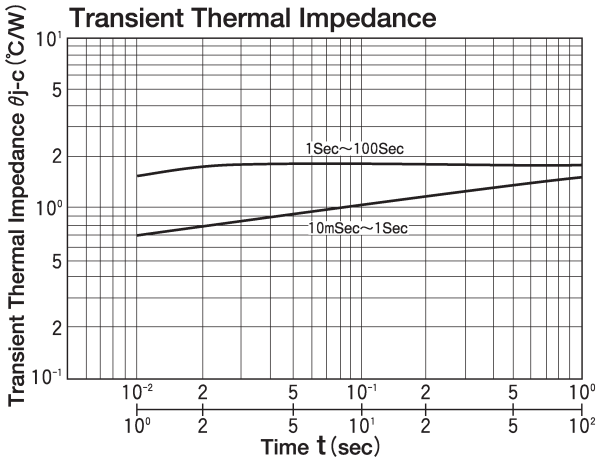
On State Current vs. Allowable Case Temperature



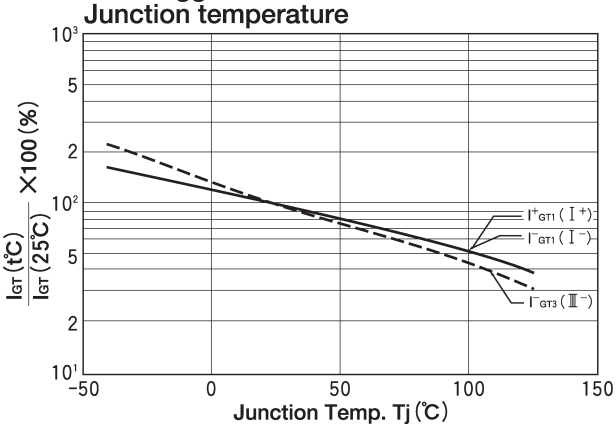
Surge On-State Current Rating (Non-Repetitive)



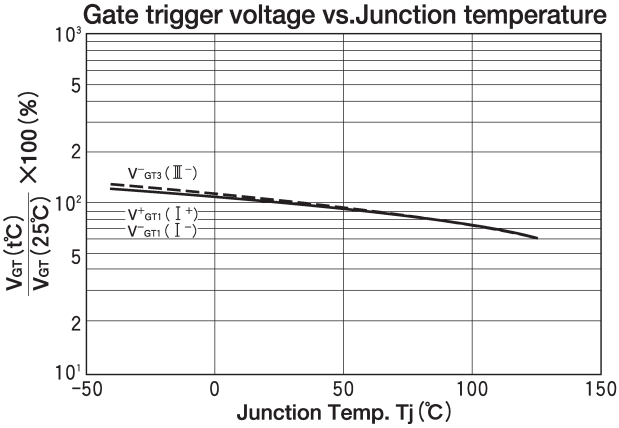
Transient Thermal Impedance



Gate trigger current vs. Junction temperature



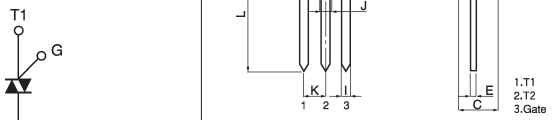
Gate trigger voltage vs.Junction temperature



TMG16C60

TMG16C60 are non-isolated triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light and heater control.

- $I_{T(RMS)}$ 16A
- High surge capability 170A
- Non-isolated type



DIM	Millimeters		
	Min	Typ	Max
A	5.58	6.40	7.49
B	8.38	8.60	8.90
C	4.40	4.50	4.70
D	1.15	1.27	1.39
E	0.35	0.45	0.60
F	9.66	10.10	10.28
G	—	16.25	—
H	—	3.83	—
I	0.75	0.85	0.95
J	1.14	1.27	1.40
K	—	2.54	—
L	12.70	13.50	14.27
M	14.48	15.00	15.87

Unit：mm

■Maximum Ratings

(Tj=25℃ unless otherwise specified)

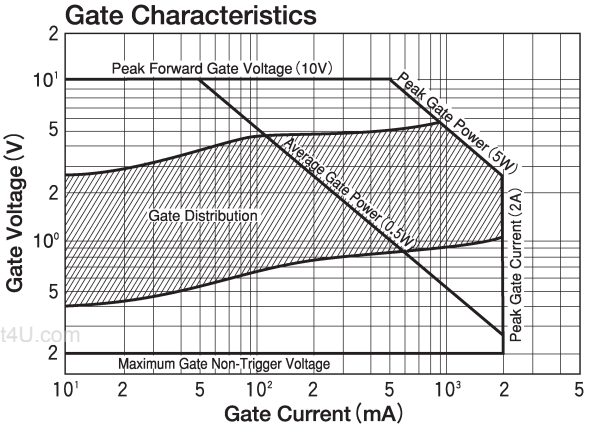
Symbol	Item	Ratings	Unit
		TMG16C60	
V_{DRM}	Repetitive Peak Off-State Voltage	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc＝98℃	16	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	155/170	A
I^2t	I^2t	Value for one cycle of surge current	120	A^2S
P_{GM}	Peak Gate Power Dissipation		5	W
$P_{G(AV)}$	Average Gate Power Dissipation		0.5	W
I_{GM}	Peak Gate Current		2	A
V_{GM}	Peak Gate Voltage		10	V
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
	Mass		2	g

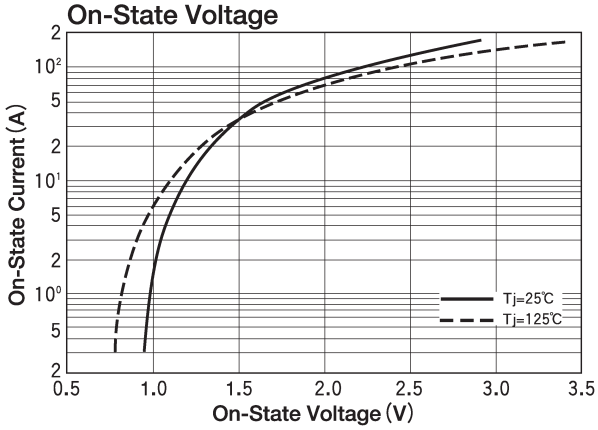
■Electrical Characteristics

Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	V_D=V_{DRM}, Single phase, half wave, Tj＝125℃			2	mA
V_{TM}		Peak On-State Voltage	I_T＝20A, Inst. measurement			1.4	V
I_{GT1}^{+}	1	Gate Trigger Current	V_D＝6V, R_L＝10Ω			30	mA
I_{GT1}^{-}	2					30	
I_{GT3}^{+}	3					—	
I_{GT3}^{-}	4					30	
V_{GT1}^{+}	1	Gate Trigger Voltage	V_D＝6V, R_L＝10Ω			1.5	V
V_{GT1}^{-}	2					1.5	
V_{GT3}^{+}	3					—	
V_{GT3}^{-}	4					1.5	
V_{GD}		Non-Trigger Gate Voltage	Tj＝125℃, V_D＝½V_{DRM}	0.2			V
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj＝125℃, (di/dt)c＝−8A/ms, V_D＝⅔V_{DRM}	10			V/μs
I_H		Holding Current			25		mA
Rth(j-c)		Thermal Impedance	Junction to case			1.4	℃/W

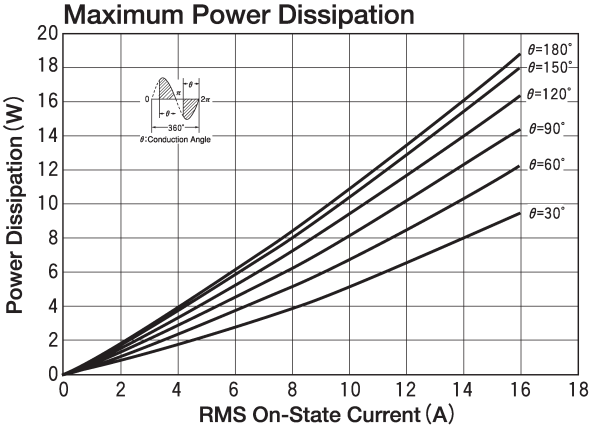
Gate Characteristics



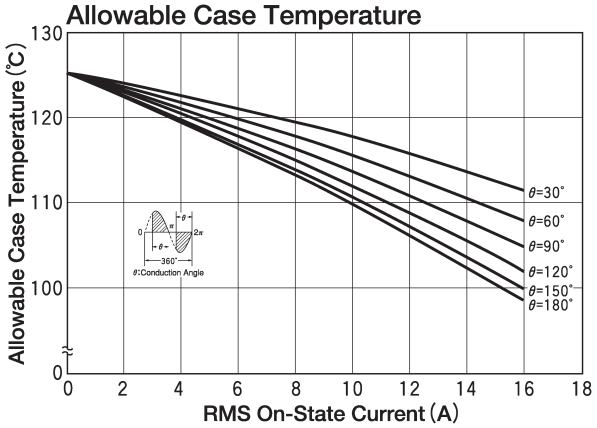
On-State Voltage



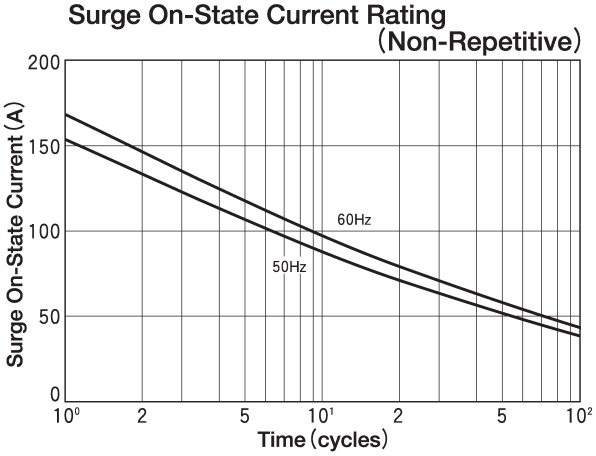
On State Current vs. Maximum Power Dissipation



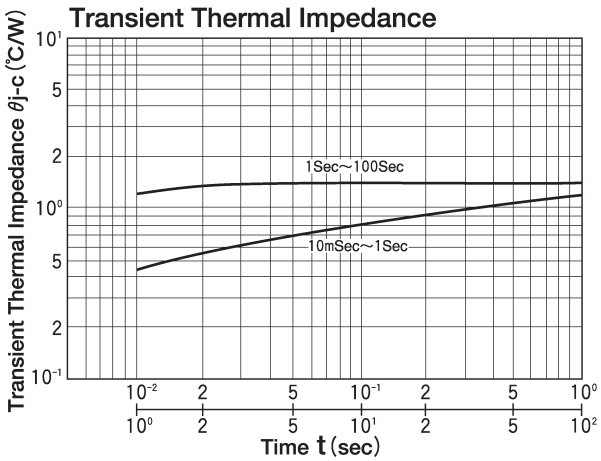
On State Current vs. Allowable Case Temperature



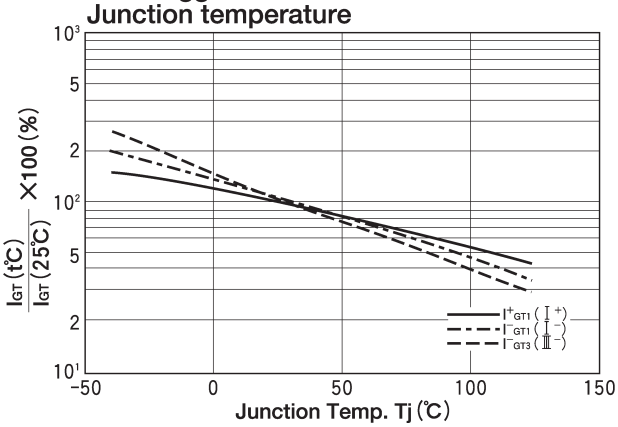
Surge On-State Current Rating (Non-Repetitive)



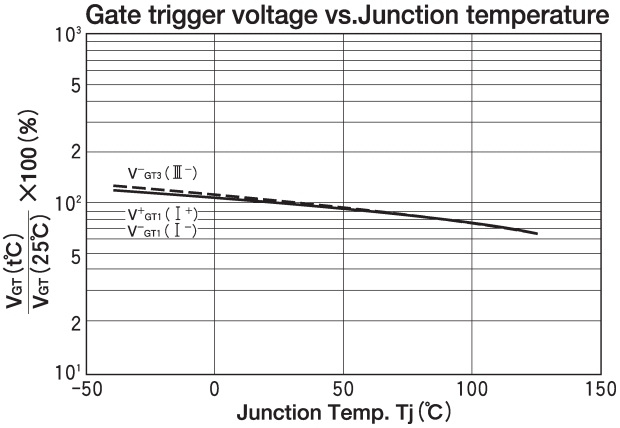
Transient Thermal Impedance



Gate trigger current vs. Junction temperature



Gate trigger voltage vs.Junction temperature



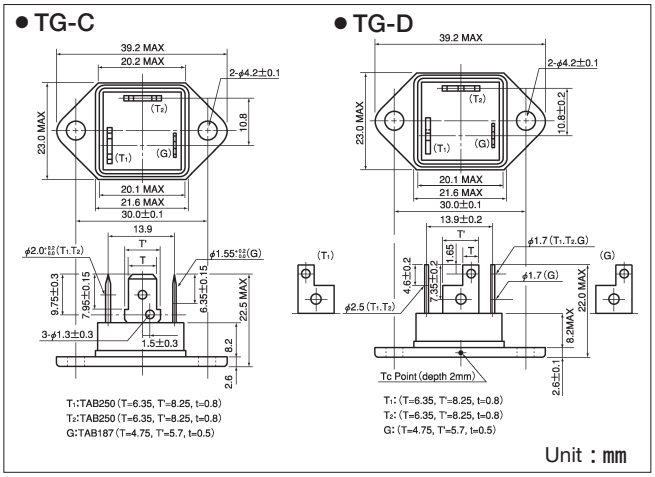
TRIAC（ISOLATED TYPE）

TG16C/D

UL;E76102 (M)

TG16C/D are isolated molded triacs suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light control and heater control.

- $I_{T(AV)}$ 16A
- High surge capability 160A
- Isolated Nounting (AC2500V)
- Tab Terminals



■Maximum Ratings

(Tj=25℃ unless otherwise specified)

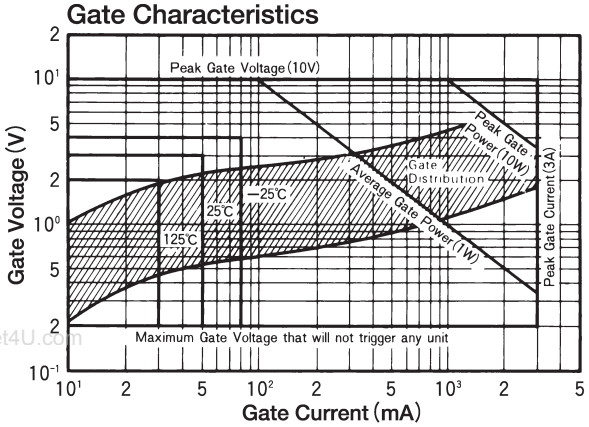
Symbol	Item	Ratings		Unit
		TG16C40	TG16C60	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc＝83℃	16	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	140/160	A
I^2t	I^2t	Value for one cycle of surge current	106	A^2S
P_{GM}	Peak Gate Power Dissipation		10	W
$P_{G(AV)}$	Average Gate Power Dissipation		1	W
I_{GM}	Peak Gate Current		3	A
V_{GM}	Peak Gate Voltage		10	V
di/dt	Critical Rate of Rise of On-State Current	I_G＝100mA, Tj＝25℃, V_D＝½V_{DRM}, dI_G/dt＝1A/μs	50	A/μs
Tj	Operating Junction Temperature		−25～+125	℃
Tstg	Storage Temperature		−40～+125	℃
V_{ISO}	Isolation Breakdown Voltage (R.M.S.)	A.C.1 minute	2500	V
	Mounting Torque (M4)	Recommended Value 1.0～1.4 (10～14)	1.5 (15)	kgf·cm
	Mass	Typical value (Excluding bolt, nut and wrapping material)	23	g

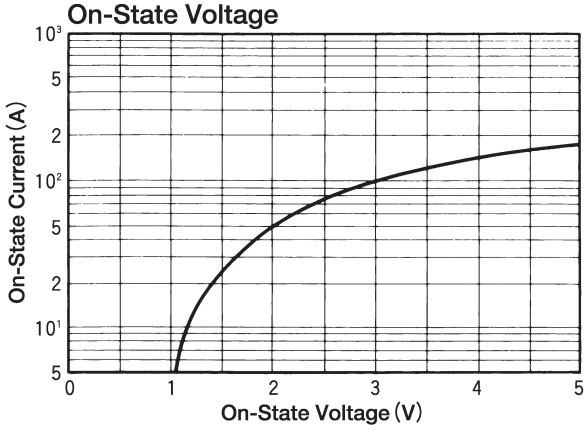
■Electrical Characteristics

Symbol		Item	Conditions	Ratings	Unit
I_{DRM}		Reptitive Peak Off-State Current, max	V_D=V_{DRM}, Single phase, half wave, Tj＝125℃	3	mA
V_{TM}		Peak On-State Voltage, max	On-State Current [√2×$I_{T(RMS)}$], Inst. measurement	1.5	V
I_{GT1}^{+}	1	Gate Trigger Current, max	Tj＝25℃, I_T＝1A, V_D＝6V	50	mA
I_{GT1}^{-}	2		Tj＝25℃, I_T＝1A, V_D＝6V	50	
I_{GT3}^{+}	3			—	
I_{GT3}^{-}	4		Tj＝25℃, I_T＝1A, V_D＝6V	50	
V_{GT1}^{+}	1	Gate Trigger Voltage, max	Tj＝25℃, I_T＝1A, V_D＝6V	3	V
V_{GT1}^{-}	2		Tj＝25℃, I_T＝1A, V_D＝6V	3	
V_{GT3}^{+}	3			—	
V_{GT3}^{-}	4		Tj＝25℃, I_T＝1A, V_D＝6V	3	
V_{GD}		Non-Trigger Gate Voltage, min	Tj＝125℃, V_D＝½V_{DRM}	0.2	V
tgt		Turn On Time, max.	$I_{T(RMS)}$, I_G＝100mA, V_D＝½V_{DRM}, Tj＝25℃, dI_G/dt＝1A/μs	10	V
dv/dt		Critical Rate of Rise on-State Voltage,min.	Tj＝125℃, V_D＝⅔V_{DRM}, Exponential wave.	50	V/μs
[dv/dt]c		Critical Rate of Rise off-State Voltage at commutation, min	Tj＝125℃, V_D＝⅔V_{DRM}, [di/dt] c＝8A/ms	6	V/μs
I_H		Holding Current, typ.	Tj＝25℃	30	mA
Rth (j-c)		Thermal Impedance, max	Junction to case	2.0	℃/W

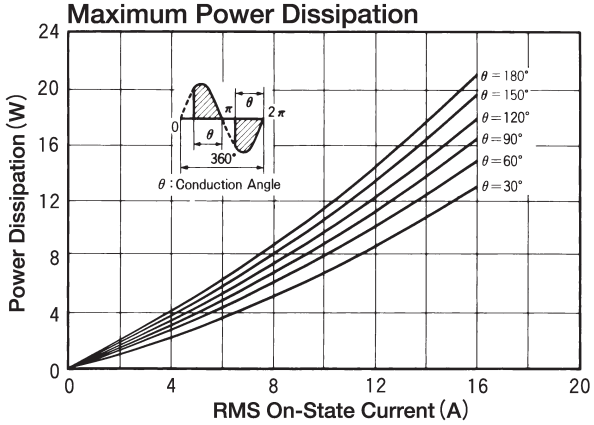
Gate Characteristics



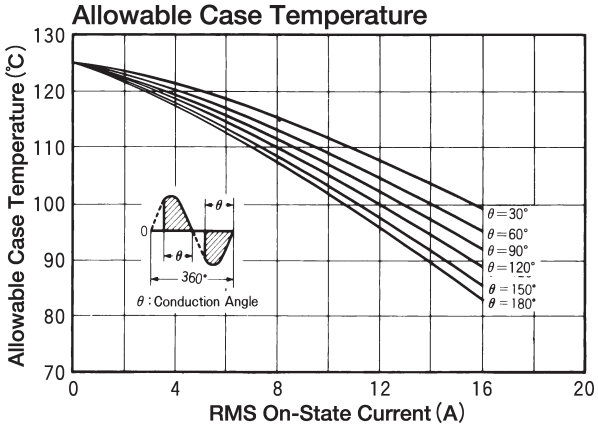
On-State Voltage



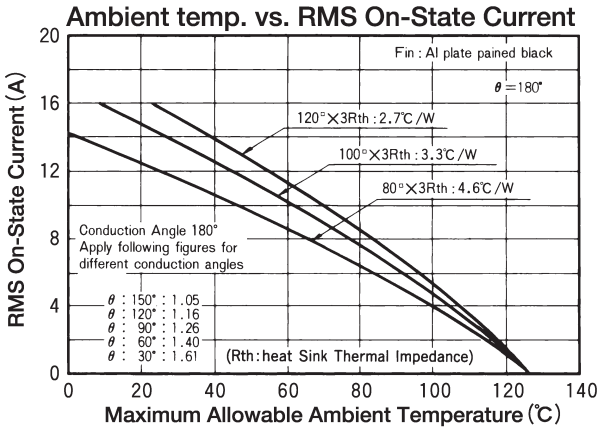
On State Current vs. Maximum Power Dissipation



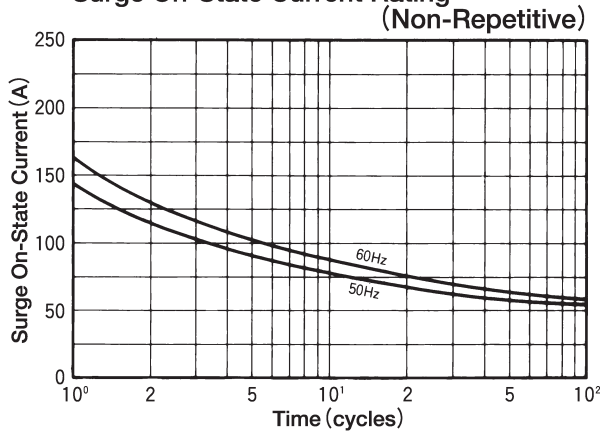
On State Current vs. Allowable Case Temperature



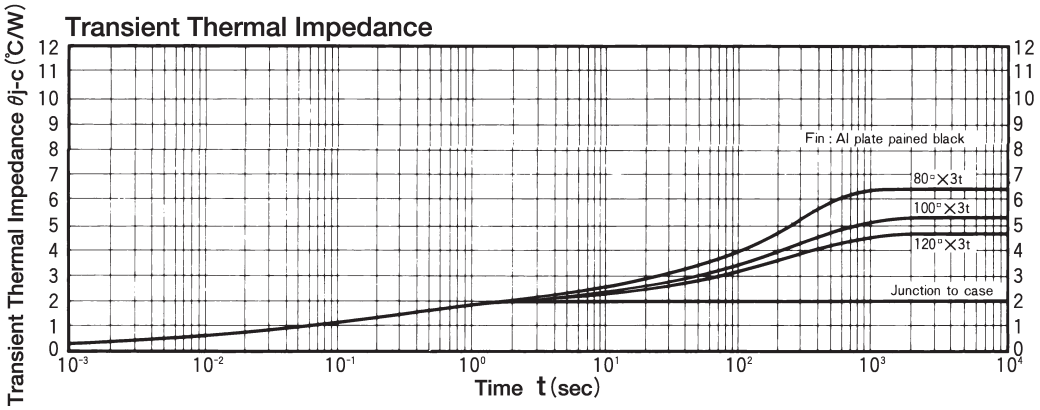
Ambient temp. vs. RMS On-State Current



Surge On-State Current Rating (Non-Repetitive)



Transient Thermal Impedance



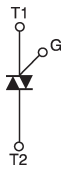
TRIAC（ISOLATED TYPE）

TG25C/E/D

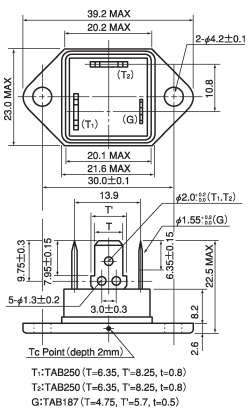
UL;E76102（M）

TG25C/E/D are isolated molded triacs suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light control and heater control.

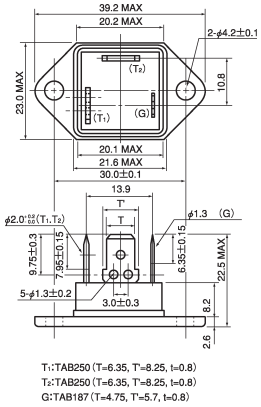
- $I_{T(AV)}$ 25A
- High surge capability 250A
- Isolated Nounting（AC2500V）
- Tab Terminals



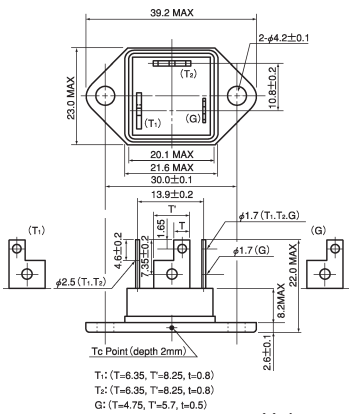
● TG-C



● TG-E



● TG-D



Unit：mm

■Maximum Ratings

（Tj=25℃ unless otherwise specified）

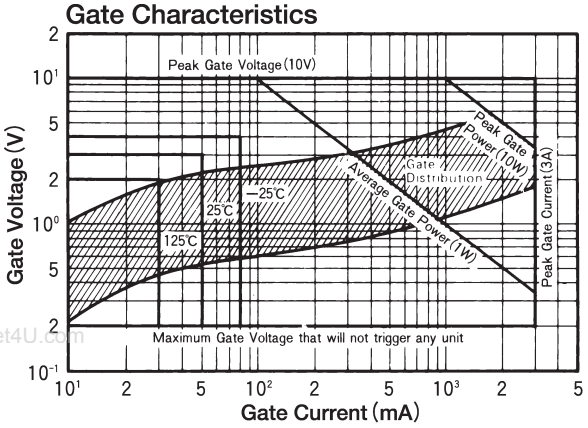
Symbol	Item	Ratings		Unit
		TG25C40	TG25C60	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V

Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc＝74℃	25	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	220/250	A
I^2t	I^2t	Value for one cycle of surge current	260	A^2S
P_{GM}	Peak Gate Power Dissipation		10	W
$P_{G(AV)}$	Average Gate Power Dissipation		1	W
I_{GM}	Peak Gate Current		3	A
V_{GM}	Peak Gate Voltage		10	V
di/dt	Critical Rate of Rise of On-State Current	I_G＝100mA, Tj＝25℃, V_D＝½V_{DRM}, dI_G/dt＝1A/μs	50	A/μs
Tj	Operating Junction Temperature		−25～+125	℃
Tstg	Storage Temperature		−40～+125	℃
V_{ISO}	Isolation Breakdown Voltage（R.M.S.）	A.C.1 minute	2500	V
	Mounting Torque（M4）	Recommended Value 1.0～1.4（10～14）	1.5（15）	kgf・cm
	Mass	Typical value （Excluding bolt, nut and wrapping material）	27	g

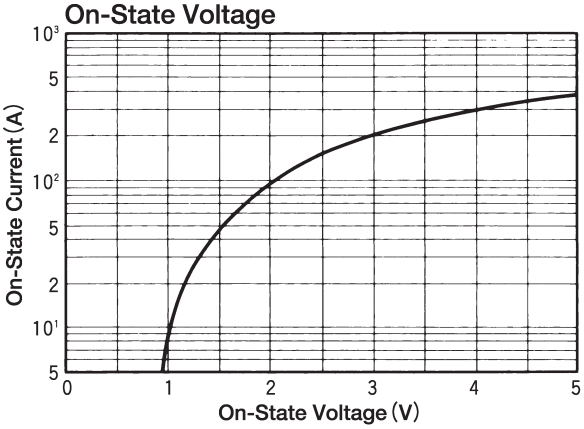
■Electrical Characteristics

Symbol		Item	Conditions	Ratings	Unit
I_{DRM}		Reptitive Peak Off-State Current, max	V_D=V_{DRM}, Single phase, half wave, Tj＝125℃	5	mA
V_{TM}		Peak On-State Voltage, max	On-State Current〔√2×$I_{T(RMS)}$〕, Inst. measurement	1.4	V
I_{GT1}^{+}	1	Gate Trigger Current, max	Tj＝25℃, I_T＝1A, V_D＝6V	50	mA
I_{GT1}^{-}	2		Tj＝25℃, I_T＝1A, V_D＝6V	50	
I_{GT3}^{+}	3			—	
I_{GT3}^{-}	4		Tj＝25℃, I_T＝1A, V_D＝6V	50	
V_{GT1}^{+}	1	Gate Trigger Voltage, max	Tj＝25℃, I_T＝1A, V_D＝6V	3	V
V_{GT1}^{-}	2		Tj＝25℃, I_T＝1A, V_D＝6V	3	
V_{GT3}^{+}	3			—	
V_{GT3}^{-}	4		Tj＝25℃, I_T＝1A, V_D＝6V	3	
V_{GD}		Non-Trigger Gate Voltage, min	Tj＝125℃, V_D＝½V_{DRM}	0.2	V
tgt		Turn On Time, max.	$I_{T(RMS)}$, I_G＝100mA, V_D＝½V_{DRM}, Tj＝25℃, dI_G/dt＝1A/μs	10	V
dv/dt		Critical Rate of Rise on-State Voltage,min.	Tj＝125℃, V_D＝⅔V_{DRM}, Exponential wave.	50	V/μs
〔dv/dt〕c		Critical Rate of Rise off-State Voltage at commutation, min	Tj＝125℃, V_D＝⅔V_{DRM}, 〔di/dt〕c＝15A/ms	6	V/μs
I_H		Holding Current, typ.	Tj＝25℃	30	mA
Rth(j-c)		Thermal Impedance, max	Junction to case	1.6	℃/W

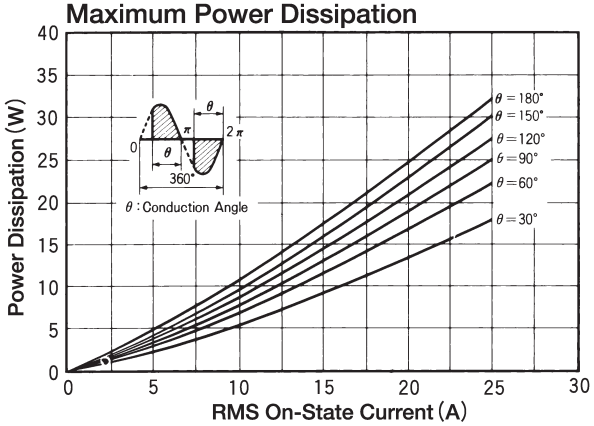
Gate Characteristics



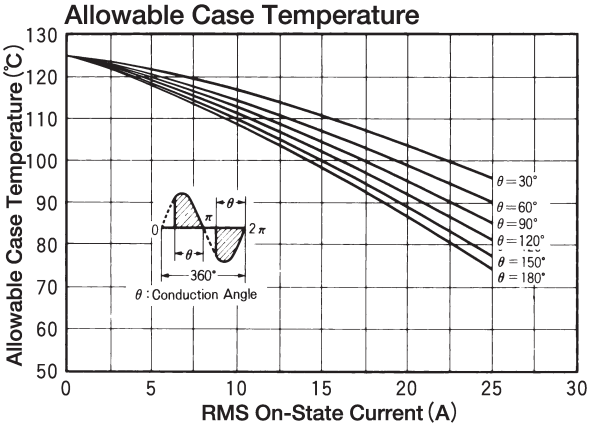
On-State Voltage



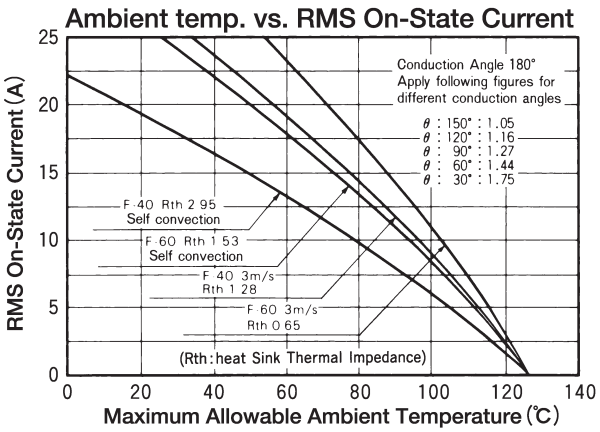
On State Current vs. Maximum Power Dissipation



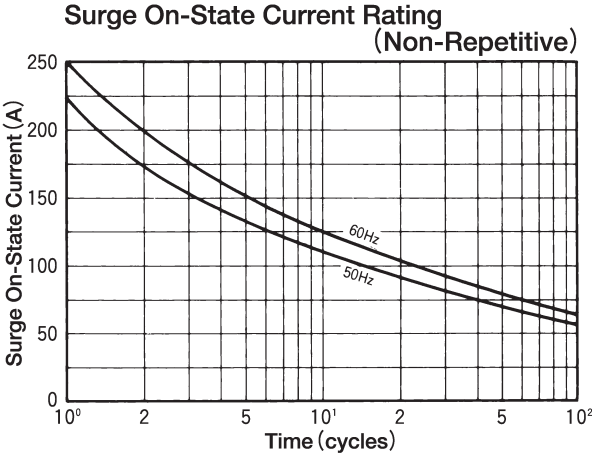
On State Current vs. Allowable Case Temperature



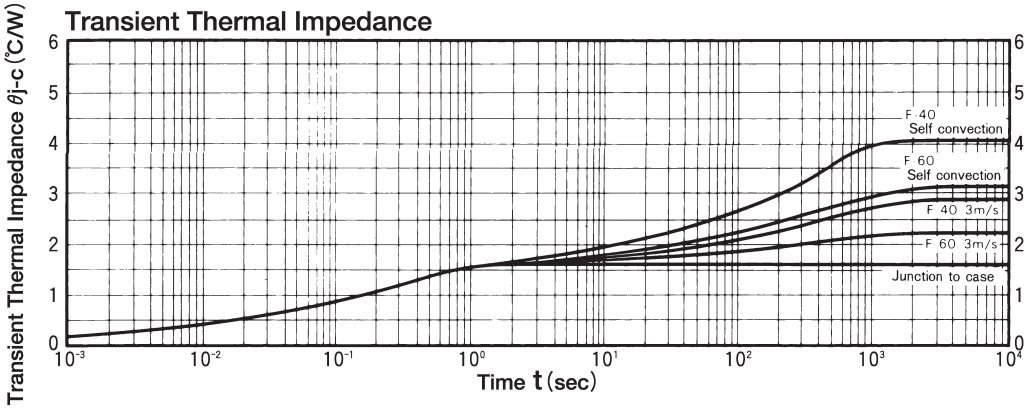
Ambient temp. vs. RMS On-State Current



Surge On-State Current Rating (Non-Repetitive)



Transient Thermal Impedance



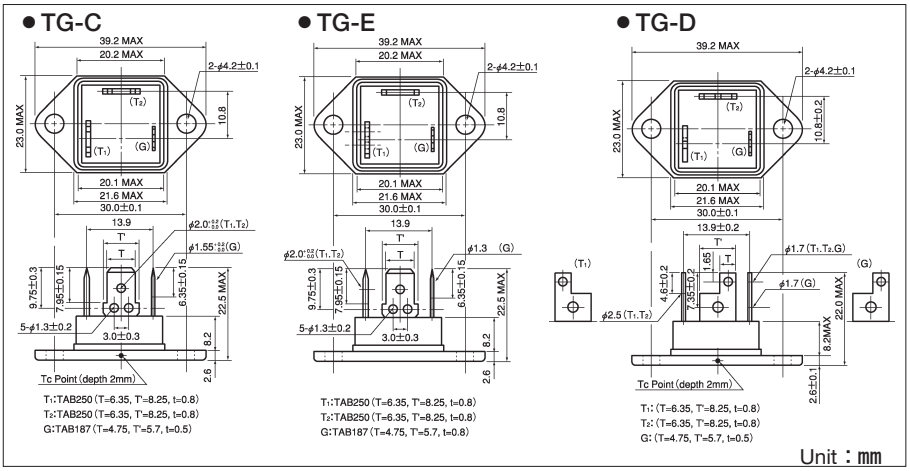
TRIAC（ISOLATED TYPE）

TG35C/E/D

UL;E76102（M）

TG35C/E/D are isolated molded triacs suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light control and heater control.

- $I_{T(AV)}$ 35A
- High surge capability 330A
- Isolated Nounting（AC2500V）
- Tab Terminals



■Maximum Ratings

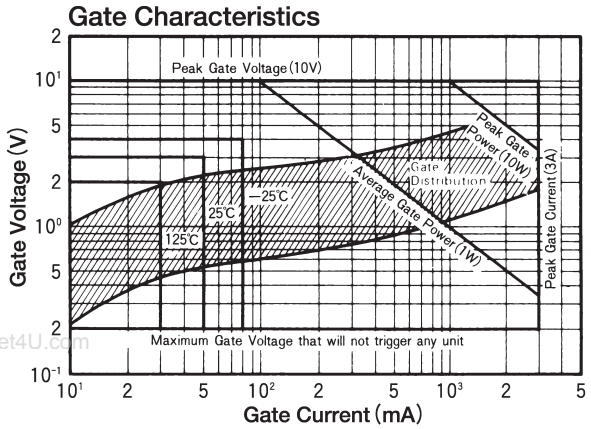
（Tj=25℃ unless otherwise specified）

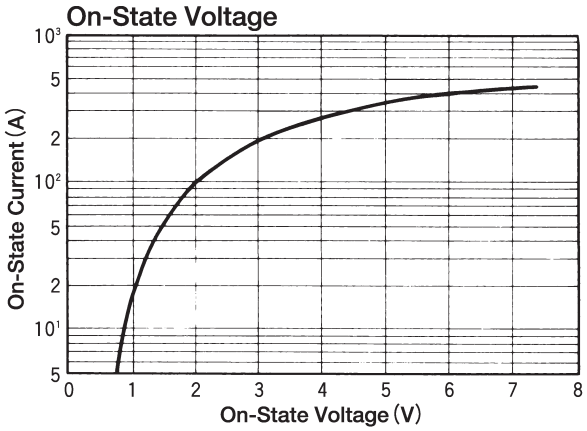
Symbol	Item	Ratings		Unit
		TG35C40	TG35C60	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V

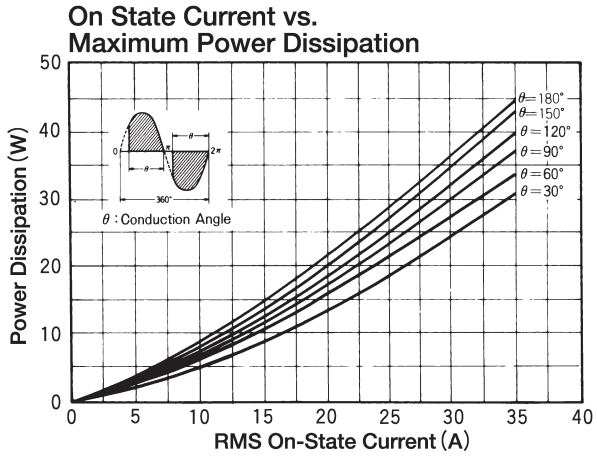
Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc＝58℃	35	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	300/330	A
I^2t	I^2t	Value for one cycle of surge current	450	A^2S
P_{GM}	Peak Gate Power Dissipation		10	W
$P_{G(AV)}$	Average Gate Power Dissipation		1	W
I_{GM}	Peak Gate Current		3	A
V_{GM}	Peak Gate Voltage		10	V
di/dt	Critical Rate of Rise of On-State Current	I_G＝100mA, Tj＝25℃, V_D＝½V_{DRM}, dI_G/dt＝1A/μs	50	A/μs
Tj	Operating Junction Temperature		−25～+125	℃
Tstg	Storage Temperature		−40～+125	℃
V_{ISO}	Isolation Breakdown Voltage（R.M.S.）	A.C.1 minute	2500	V
	Mounting Torque（M4）	Recommended Value 1.0～1.4（10～14）	1.5（15）	kgf・cm
	Mass	Typical value （Excluding bolt, nut and wrapping material）	23	g

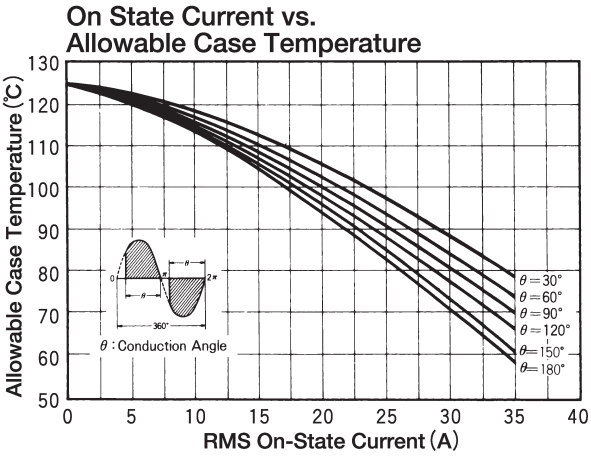
■Electrical Characteristics

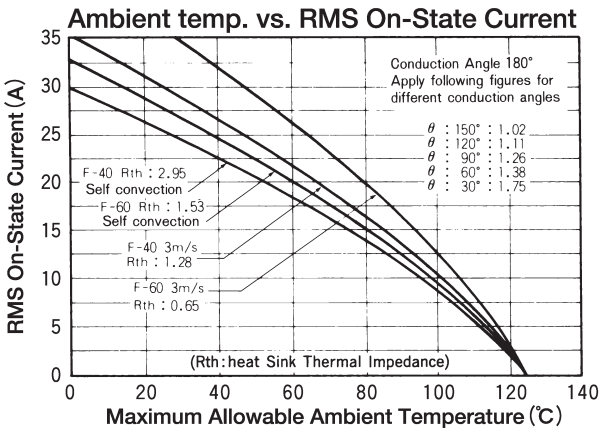
Symbol		Item	Conditions	Ratings	Unit
I_{DRM}		Reptitive Peak Off-State Current, max	V_D=V_{DRM}, Single phase, half wave, Tj＝125℃	5	mA
V_{TM}		Peak On-State Voltage, max	On-State Current〔√2×$I_{T(RMS)}$〕, Inst. measurement	1.4	V
I_{GT1}^{+}	1	Gate Trigger Current, max	Tj＝25℃, I_T＝1A, V_D＝6V	50	mA
I_{GT1}^{-}	2		Tj＝25℃, I_T＝1A, V_D＝6V	50	
I_{GT3}^{+}	3			—	
I_{GT3}^{-}	4		Tj＝25℃, I_T＝1A, V_D＝6V	50	
V_{GT1}^{+}	1	Gate Trigger Voltage, max	Tj＝25℃, I_T＝1A, V_D＝6V	3	V
V_{GT1}^{-}	2		Tj＝25℃, I_T＝1A, V_D＝6V	3	
V_{GT3}^{+}	3			—	
V_{GT3}^{-}	4		Tj＝25℃, I_T＝1A, V_D＝6V	3	
V_{GD}		Non-Trigger Gate Voltage, min	Tj＝125℃, V_D＝½V_{DRM}	0.2	V
tgt		Turn On Time, max.	$I_{T(RMS)}$, I_G＝100mA, V_D＝½V_{DRM}, Tj＝25℃, dI_G/dt＝1A/μs	10	V
dv/dt		Critical Rate of Rise on-State Voltage,min.	Tj＝125℃, V_D＝⅔V_{DRM}, Exponential wave.	20	V/μs
〔dv/dt〕c		Critical Rate of Rise off-State Voltage at commutation, min	Tj＝125℃, V_D＝⅔V_{DRM}, 〔di/dt〕c＝15A/ms	5	V/μs
I_H		Holding Current, typ.	Tj＝25℃	30	mA
Rth（j-c）		Thermal Impedance, max	Junction to case	1.5	℃/W

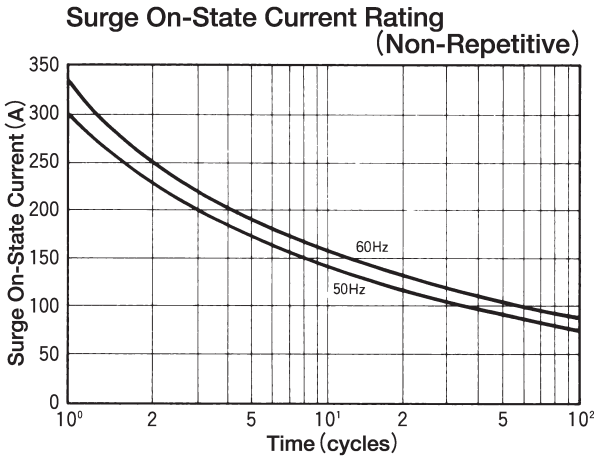


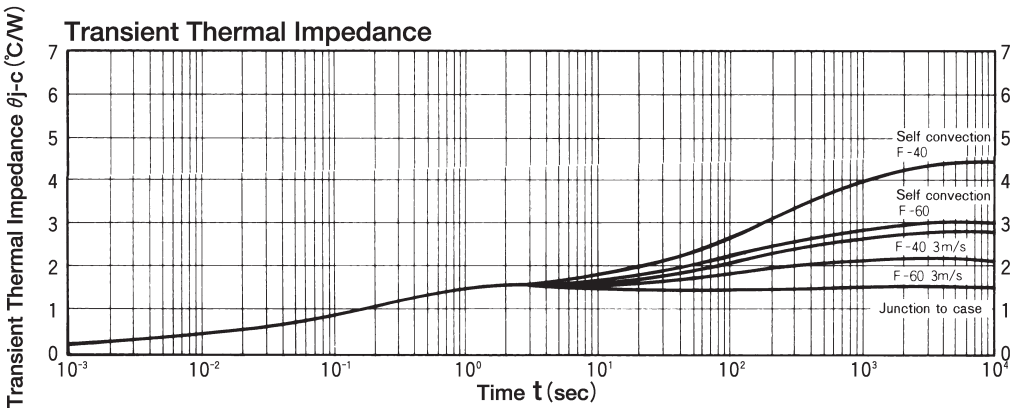










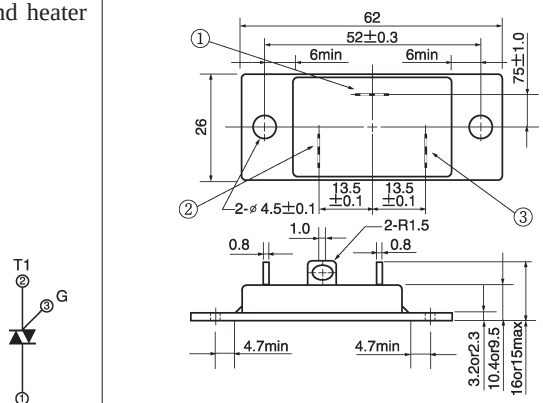


TRIAC（ISOLATED TYPE）

TG70AA40/60

TG70AA40/60 are isolated mould triac suitable for wide range of applications like copier, microwave oven, solid state switch, motor control, light control and heater control.

- $I_{T(AV)}$ 70A
- High surge capability 600A
- Isolated Nounting（AC650V）
- Tab Terminals



■Maximum Ratings

（Tj=25℃ unless otherwise specified）

Symbol	Item	Ratings		Unit
		TG70AA40	TG70AA60	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V
V_{DSM}	Non-Repetitive Peak Off-State Voltage	450	650	V

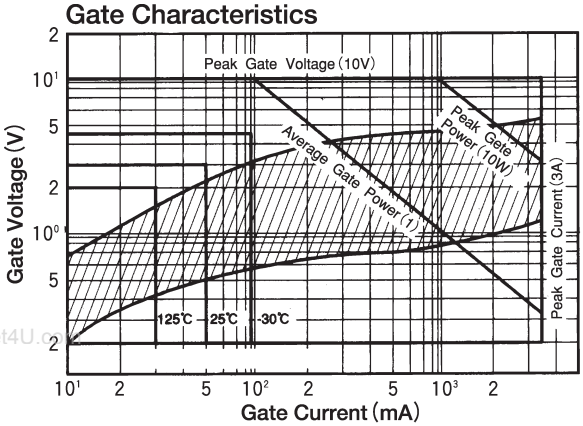
Symbol	Item	Conditions	Ratings	Unit
$I_{T(RMS)}$	R.M.S. On-State Current	Tc=58℃	70	A
I_{TSM}	Surge On-State Current	One cycle, 50Hz/60Hz, peak, non-repetitive	1080/1200	A
I^2t	I^2t		6000	A^2S
P_{GM}	Peak Gate Power Dissipation		10	W
$P_{G(AV)}$	Average Gate Power Dissipation		1	W
I_{GM}	Peak Gate Current		3	A
V_{GM}	Peak Gate Voltage		10	V
di/dt	Critical Rate of Rise of On-State Current	I_G=100mA, Tj=25℃, $V_D=\frac{1}{2}V_{DRM}$, dI_G/dt=1A/μs	50	A/μs
Tj	Operating Junction Temperature		−40～+125	℃
Tstg	Storage Temperature		−40～+125	℃
V_{ISO}	Isolation Breakdown Voltage（R.M.S.）	A.C.1 minute	2500	V
	Mounting Torque（Mounting M4）	Recommended Value 1.0～1.4（10～14）	1.5（15）	N·m (kgf·cm)
	Mass			g

■Electrical Characteristics

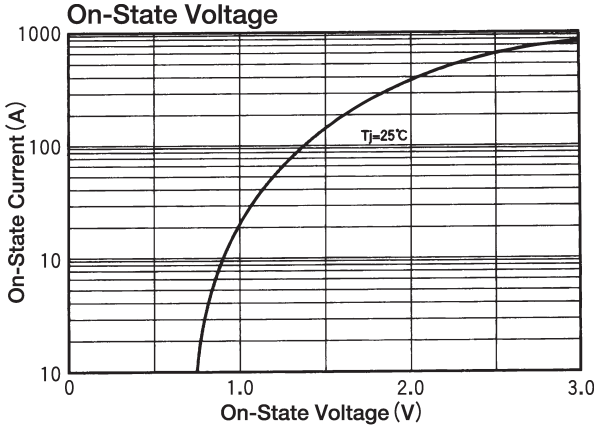
Symbol		Item	Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{DRM}		Reptitive Peak Off-State Current	$V_D=V_{DRM}$, Single phase, half wave, Tj=125℃			10	mA
V_{TM}		Peak On-State Voltage	On-State Current, 100A, I_T=25A, Inst. measurement			1.35	V
I_{GT1}^{+}	1	Gate Trigger Current	Tj=25℃, I_T=1A, V_D=6V			50	mA
I_{GT1}^{-}	2		Tj=25℃, I_T=1A, V_D=6V			50	
I_{GT3}^{+}	3						
I_{GT3}^{-}	4		Tj=25℃, I_T=1A, V_D=6V			50	
V_{GT1}^{+}	1	Gate Trigger Voltage	Tj=25℃, I_T=1A, V_D=6V			3	V
V_{GT1}^{-}	2		Tj=25℃, I_T=1A, V_D=6V			3	
V_{GT3}^{+}	3						
V_{GT3}^{-}	4		Tj=25℃, I_T=1A, V_D=6V			3	
V_{GD}		Non-Trigger Gate Voltage	Tj=125℃, $V_D=\frac{1}{2}V_{DRM}$	0.2			V
dv/dt		Critical Rate of Rise on-State Voltage,min.	Tj=125℃, $V_D=\frac{2}{3}V_{DRM}$, Exponential wave.	50			V/μs
(dv/dt)c		Critical Rate of Rise off-State Voltage at commutation	Tj=125℃, $V_D=\frac{2}{3}V_{DRM}$, (di/dt) c=8A/ms	6			V/μs
I_H		Holding Current	Tj=25℃		50	100	mA
Rth(j-c)		Thermal Impedance	Junction to case			0.83	℃/W

SanRex

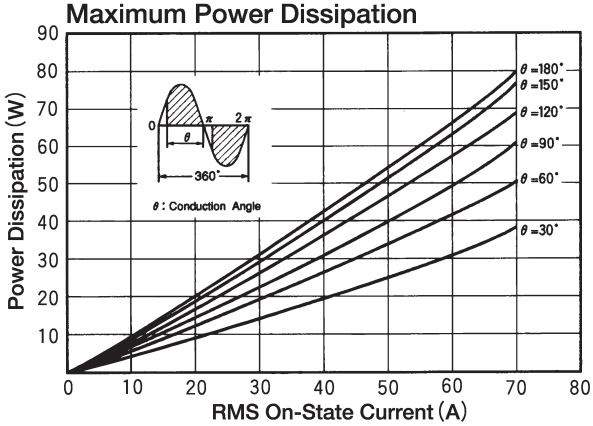
Gate Characteristics



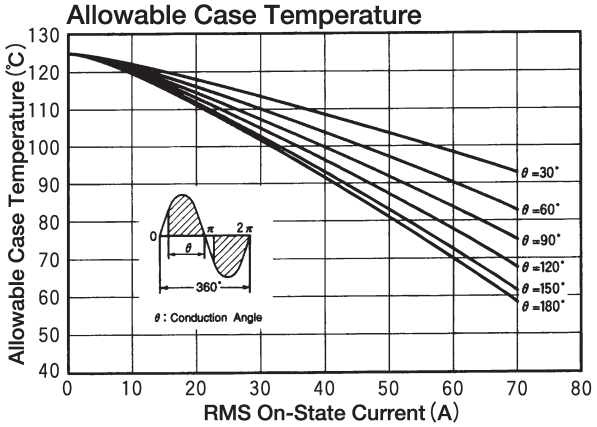
On-State Voltage



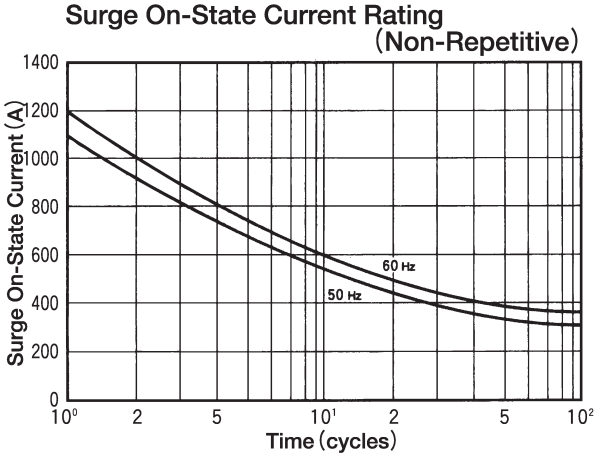
On State Current vs. Maximum Power Dissipation



On State Current vs. Allowable Case Temperature



Surge On-State Current Rating (Non-Repetitive)



Transient Thermal Impedance